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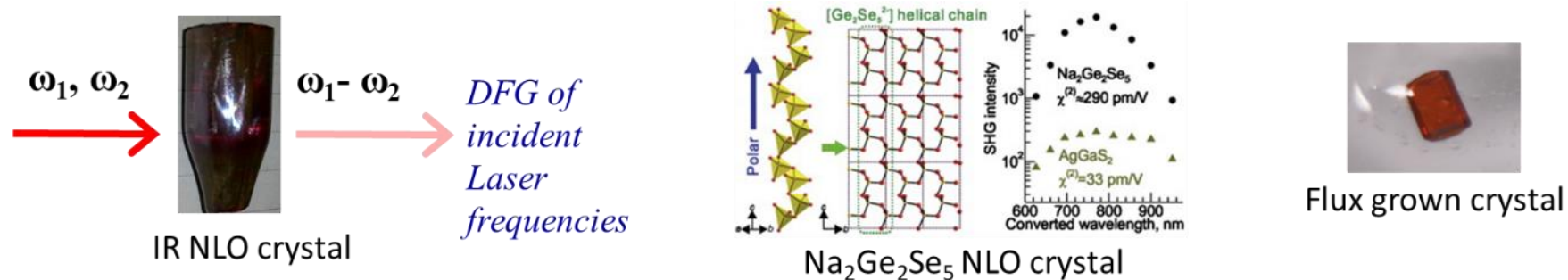
Low-dimensional materials for high-efficiency/high-power nonlinear optical applications in the infrared

Mercouri Kanatzidis
Northwestern University



Overarching goal

- Next generation of NLO crystals for IR
- Realize a deeper understanding of the relationship between crystal structure, dimensionality and difference frequency generation (DFG), especially in the IR region
- Transform the way high performance NLO materials are designed thereby accelerating future discoveries in the field and enabling associated technologies.
- Leverage the new insights to create a new generation of top performing NLO IR materials with wide optical gaps and high laser damage threshold (LDT).
- Train graduate students and postdocs in the art and science of NLO



Generation of new IR: difference frequency generation ($\omega_1 - \omega_2$)



Project objectives

- Synthesize highly pure chalcogenide materials with non-centrosymmetric structures and strong NLO response,
- Measure all fundamental NLO properties of the crystals
- Demonstrate crystal exhibit excellent wavelength tunability over a very broad IR range ($\sim 1 - 20 \mu\text{m}$)
- Assess laser damage threshold of most promising materials and down-select to the top one of two best performing materials.
- Provide crystals to the AFRL Dayton group for further evaluation and feedback

Nonlinear optical phenomena

Taylor series expansion of the dielectric polarization density (electric dipole moment per unit volume) $\mathbf{P}(t)$ at time t in terms of the electric field $\mathbf{E}(t)$, $\chi^{(1)}, \chi^{(2)}, \chi^{(3)}$ susceptibilities of the medium

$$\mathbf{P}(t) = \epsilon_0 (\chi^{(1)} \mathbf{E}(t) + \chi^{(2)} \mathbf{E}^2(t) + \chi^{(3)} \mathbf{E}^3(t) + \dots),$$

where the coefficients $\chi^{(n)}$ are the n -th-order susceptibilities of the medium, and the presence of such a term is generally referred to as an n -th-order nonlinearity.

Only non-centrosymmetric crystals have $\chi^{(2)}$

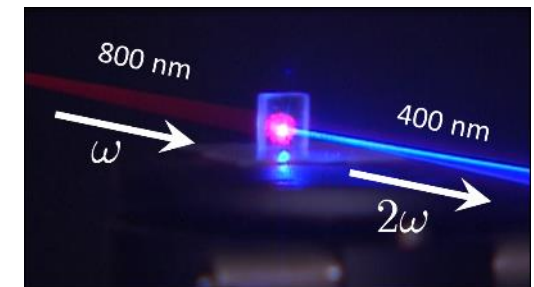
Generation of new UV: second harmonic generation ($2\omega_1$)

sum frequency generation ($\omega_1 + \omega_2$)

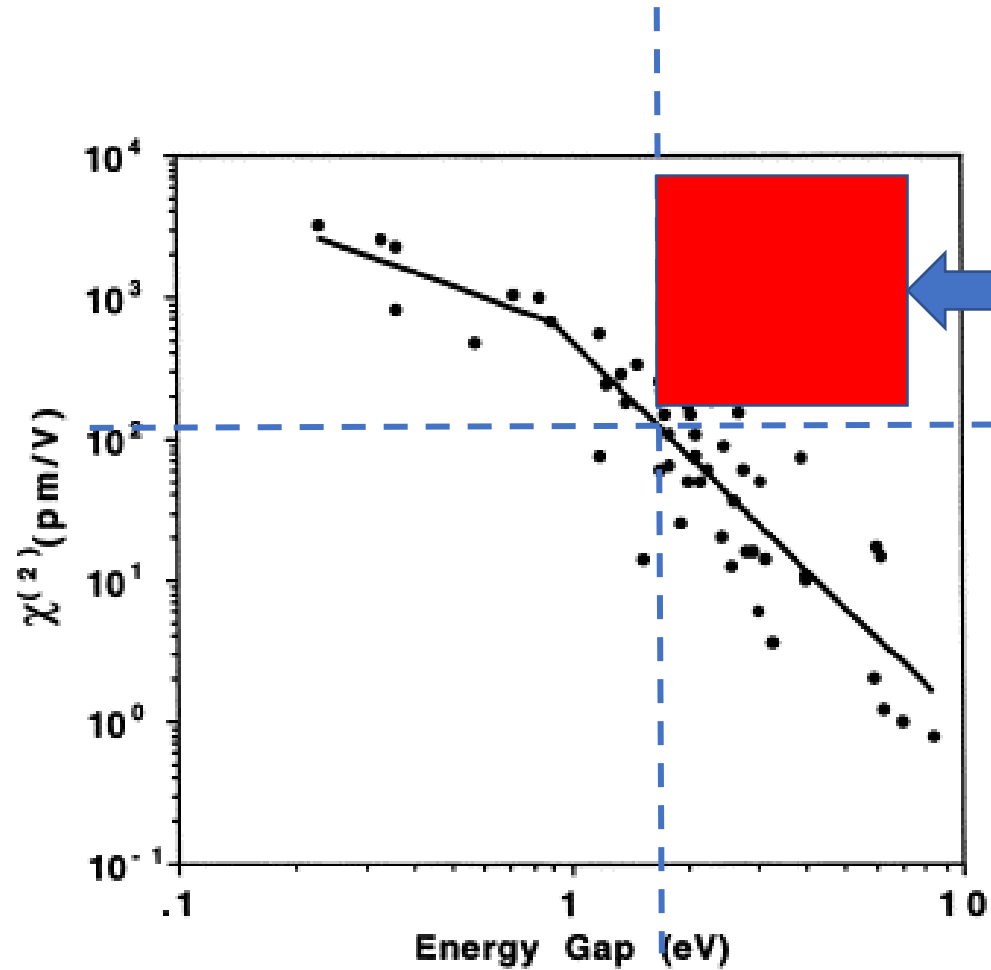
Generation of new IR: difference frequency generation ($\omega_1 - \omega_2$)

Virtual 2-photon process

in a noncentrosymmetric medium



Overview Relating $\chi^{(2)}$ to bandgap E_g



We seek new materials in this box

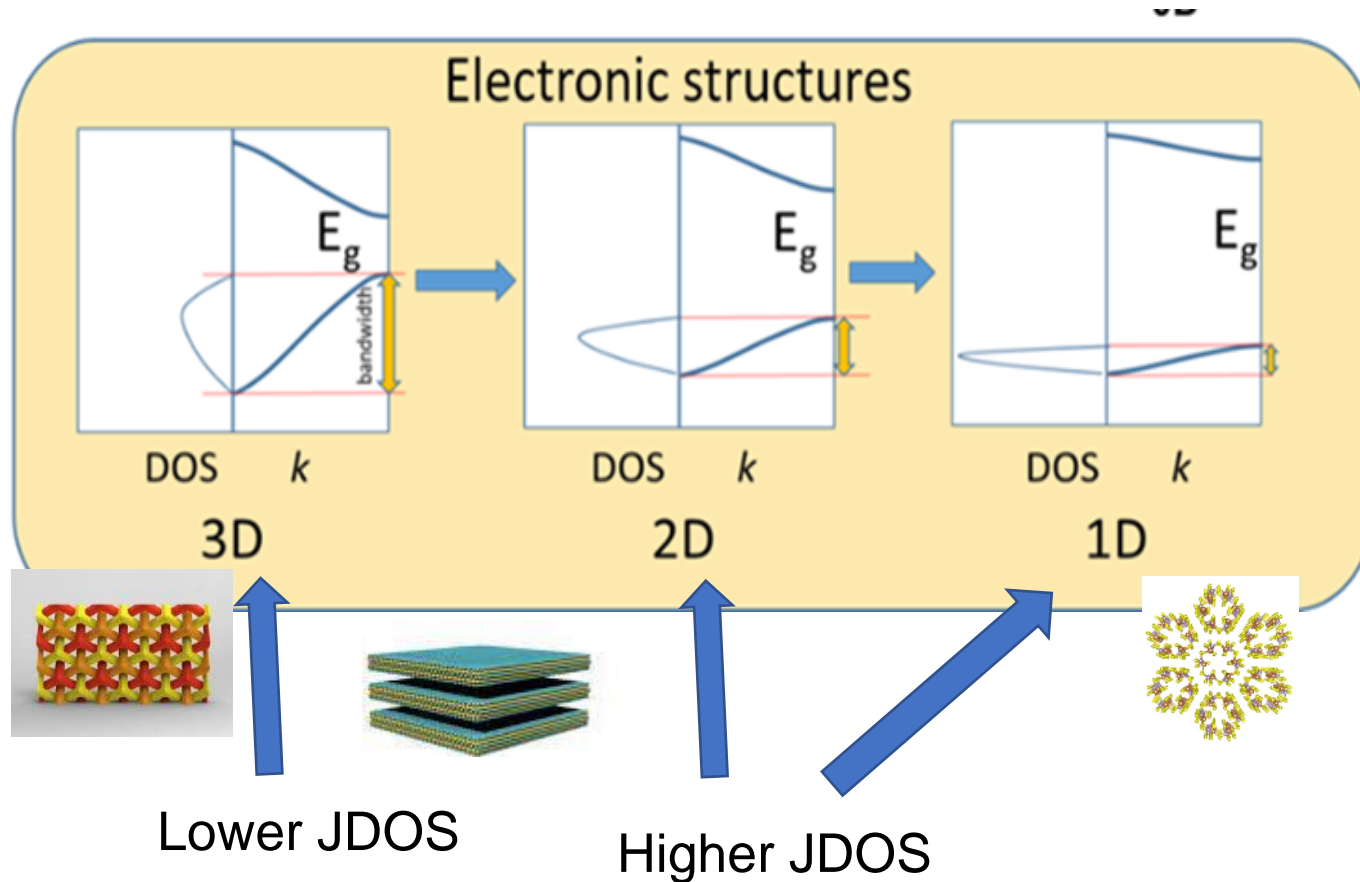
Jackson, A. G. et al. *Infrared Phys. Technol.* **1997**, *38*, 233.

Bandgaps of interest: $E_g > 1.7-2.0$ eV



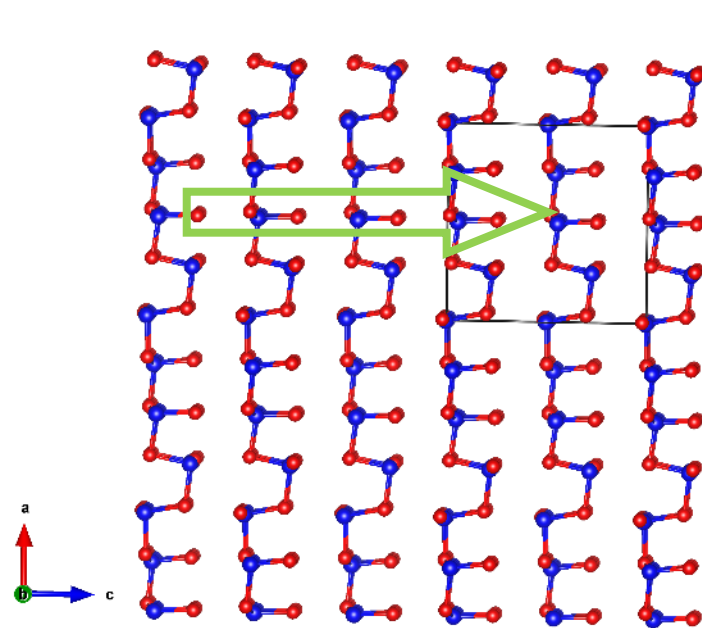
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Our focus is on low-dimensional materials



- Theory predicts:
 - low-dimensional structures with polarizable elements (e.g. chalcogens: S, Se, Te) have higher joint density of states (JDOS) than corresponding three-dimensional (3D) structures
 - Result: higher NLO optical responses.

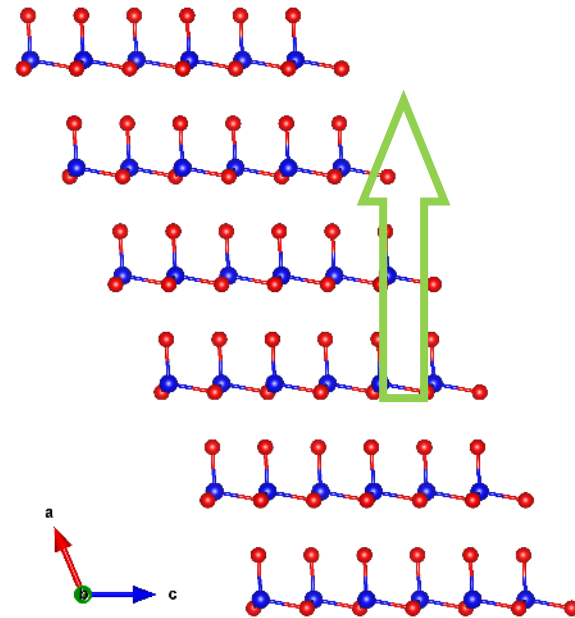
Polar crystals: $AAsQ_2$ ($A = Li$ and Na ; $Q = S, Se$)



Pc (noncentrosymmetric; NC)

$a = 11.682 \text{ \AA}$, $b = 5.902 \text{ \AA}$, $c = 11.823 \text{ \AA}$

$\beta = 90.44^\circ$



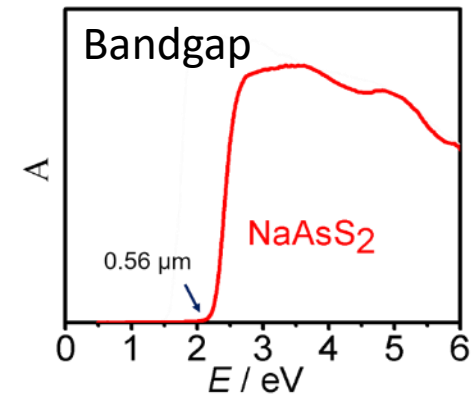
Cc (noncentrosymmetric; NC)

$a = 12.287 \text{ \AA}$, $b = 5.541 \text{ \AA}$, $c = 5.553 \text{ \AA}$

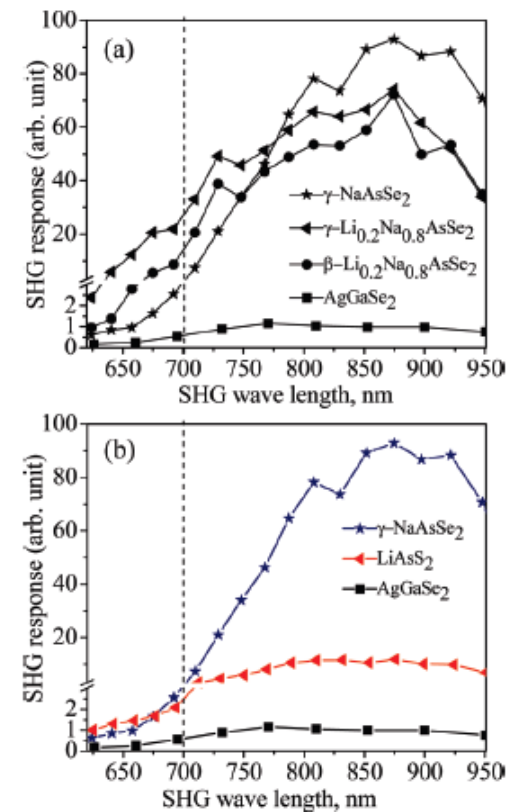
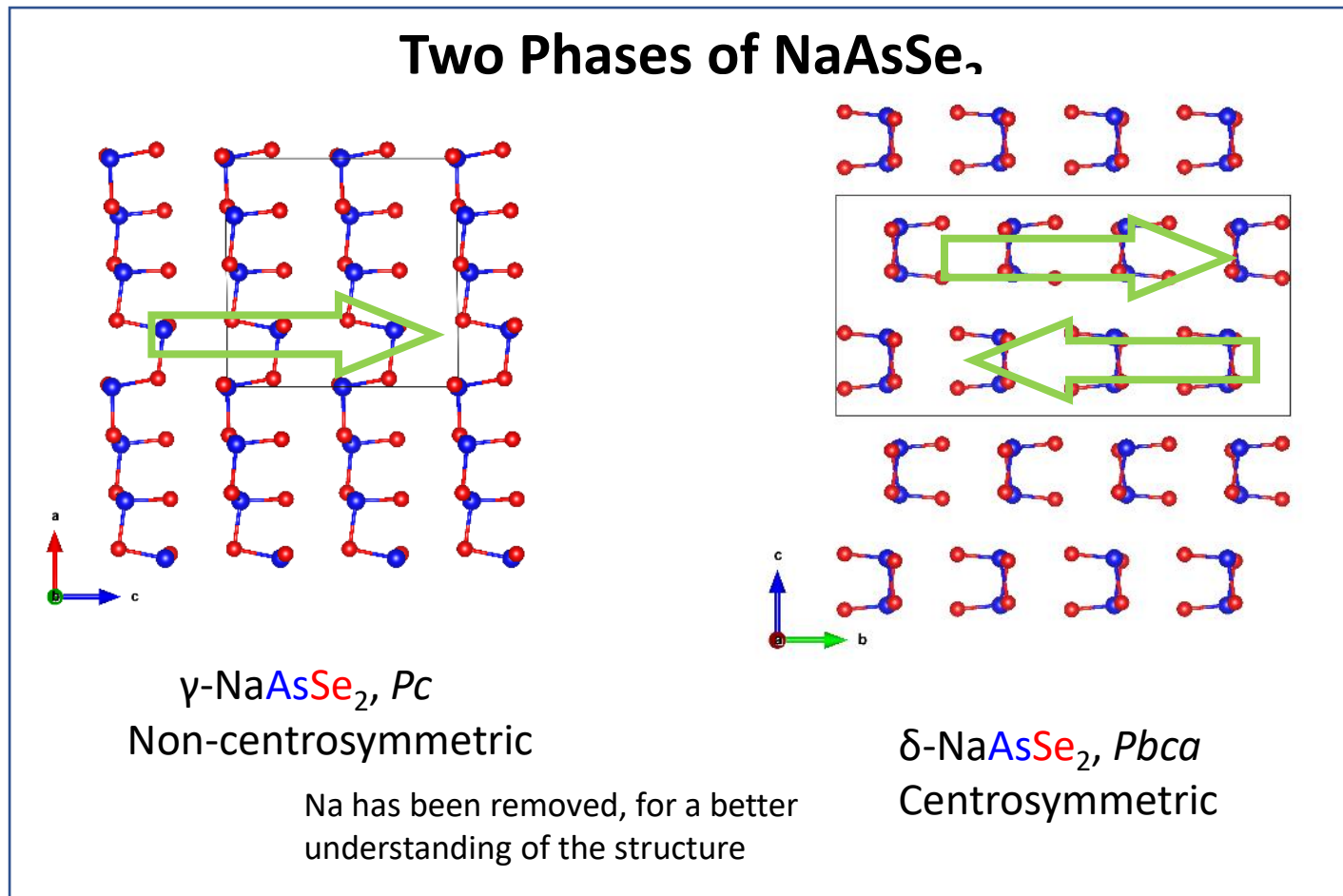
$\beta = 113.12^\circ$

Sulfide	Space group	Selenide	Space group
$LiAsS_2$	Cc	$LiAsSe_2$	Cc
$NaAsS_2$	$P2_1/b$	$\gamma\text{-NaAsSe}_2$	Pc
		$\delta\text{-NaAsSe}_2$	$Pbca$
$Li_{0.6}Na_{0.4}AsS_2$	Cc	$\beta\text{-Li}_{0.2}Na_{0.8}AsSe_2$	Cc
		$\gamma\text{-Li}_{0.2}Na_{0.8}AsSe_2$	Pc

Effect on $NaAsSe_2$ structure due to Li Substitution



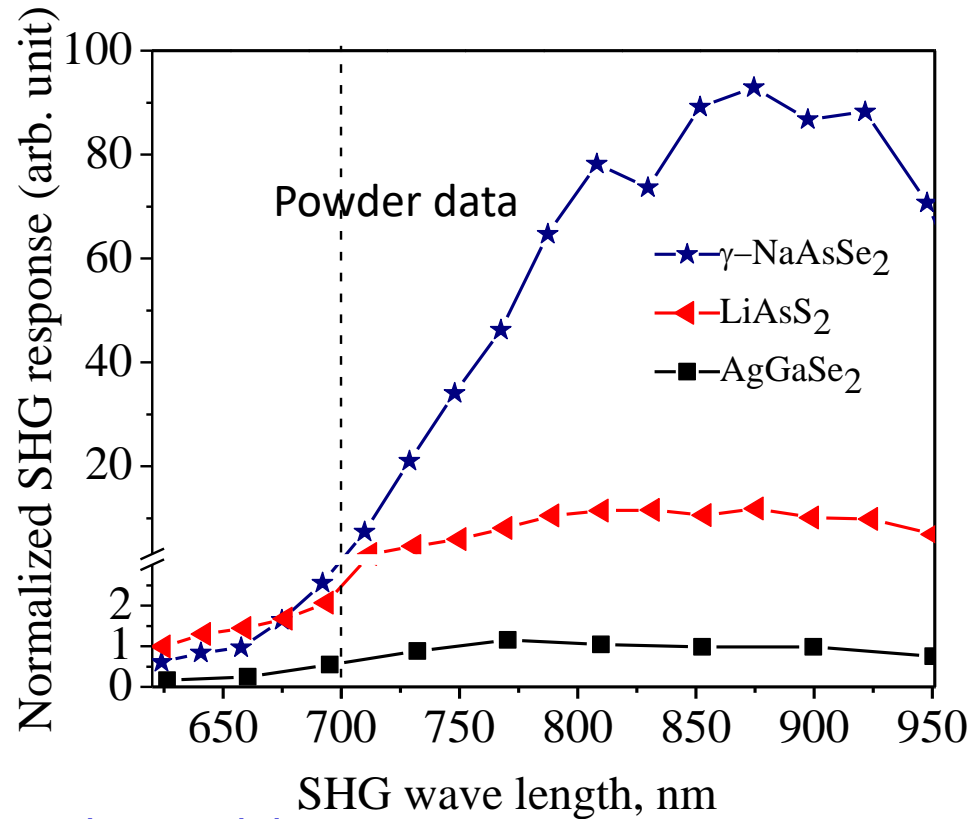
Noncentrosymmetric NaAsSe₂



SHG intensity:
 γ -NaAsSe₂
 75 x AgGaSe₂
 γ -Li_{0.2}Na_{0.8}AsSe₂
 65 x AgGaSe₂
 β -Li_{0.2}Na_{0.8}AsSe₂
 55 x AgGaSe₂



AAsS₂ and AAsSe₂: Very promising materials with strong SHG reported by our group



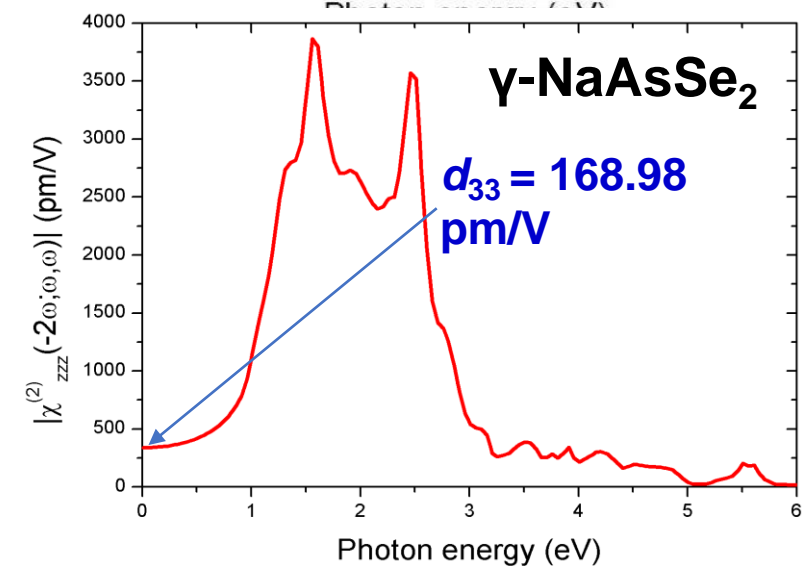
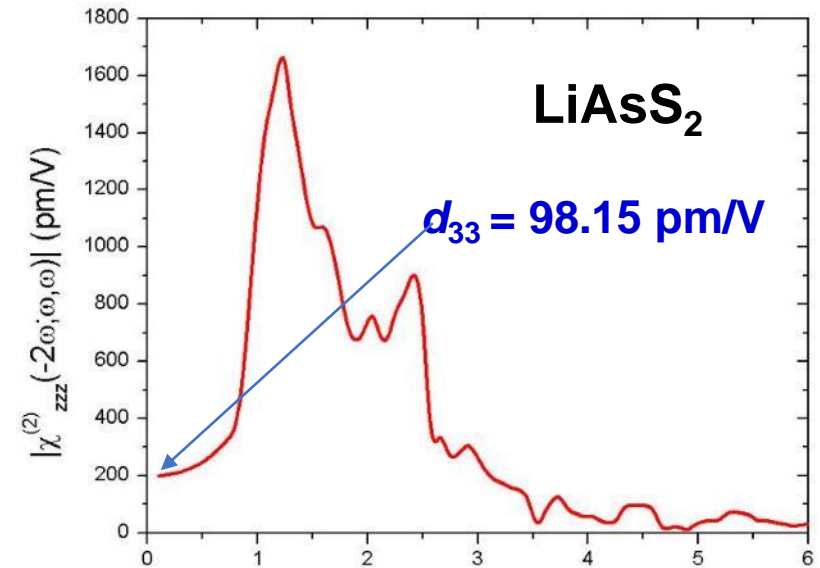
Benchmark materials

AgGaSe₂: 32 pm/V

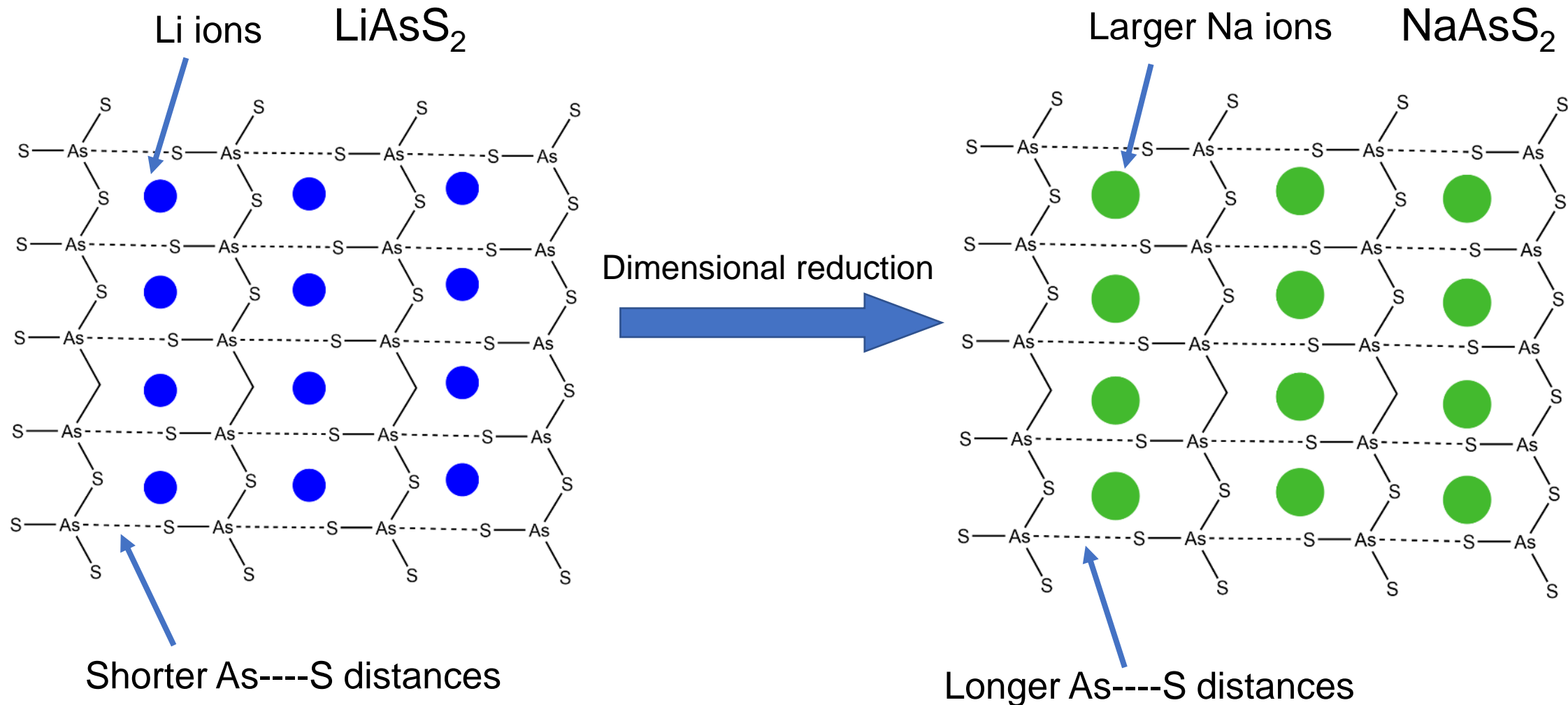
GaAs: 91 pm/V

ZnGeP₂ 75 pm/V

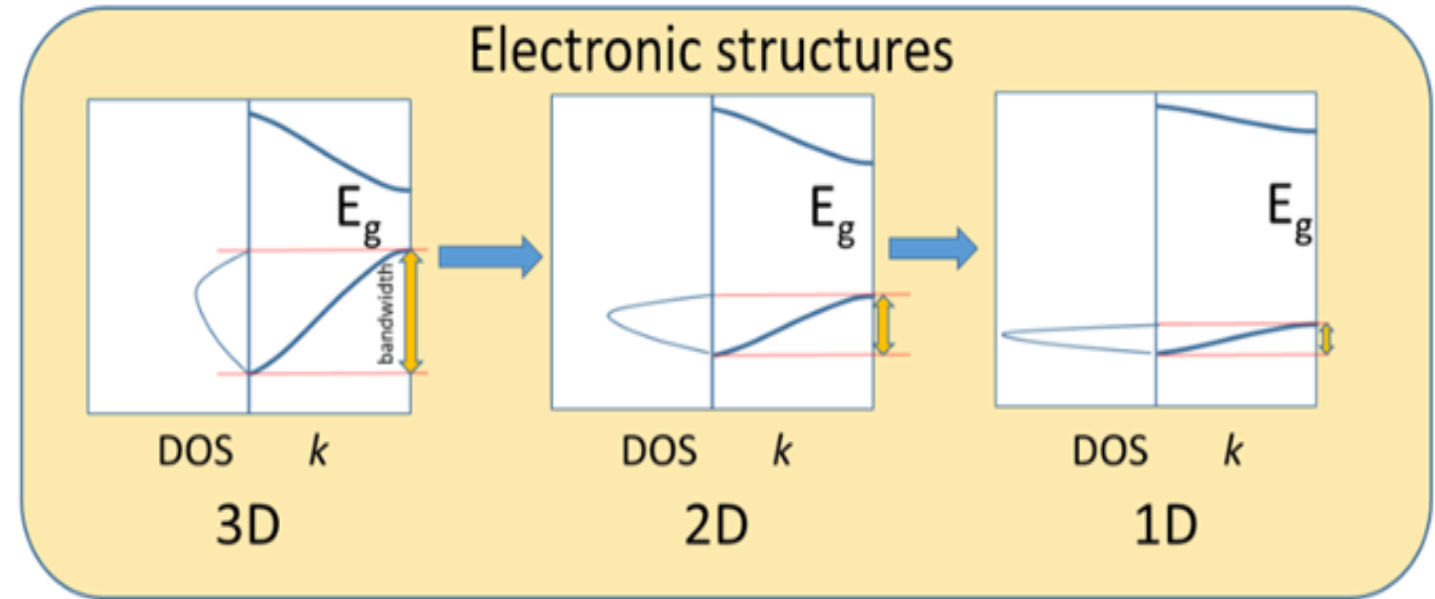
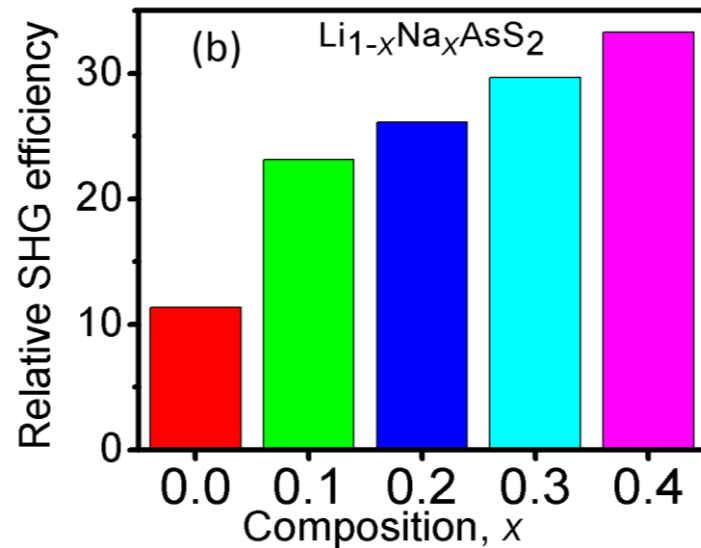
Highest SHG susceptibility (χ)
(with band-gap >1.5 eV)



$\text{Li}_{1-x}\text{Na}_x\text{AsS}_2$: Na addition reduces interchain $[\text{AsS}_2]^{1-}$ interactions...

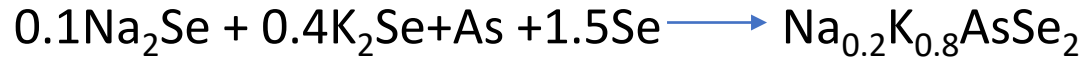


Li_{1-x}Na_xAsS₂: Na addition reduces interchain [AsS₂]¹⁻ interactions...



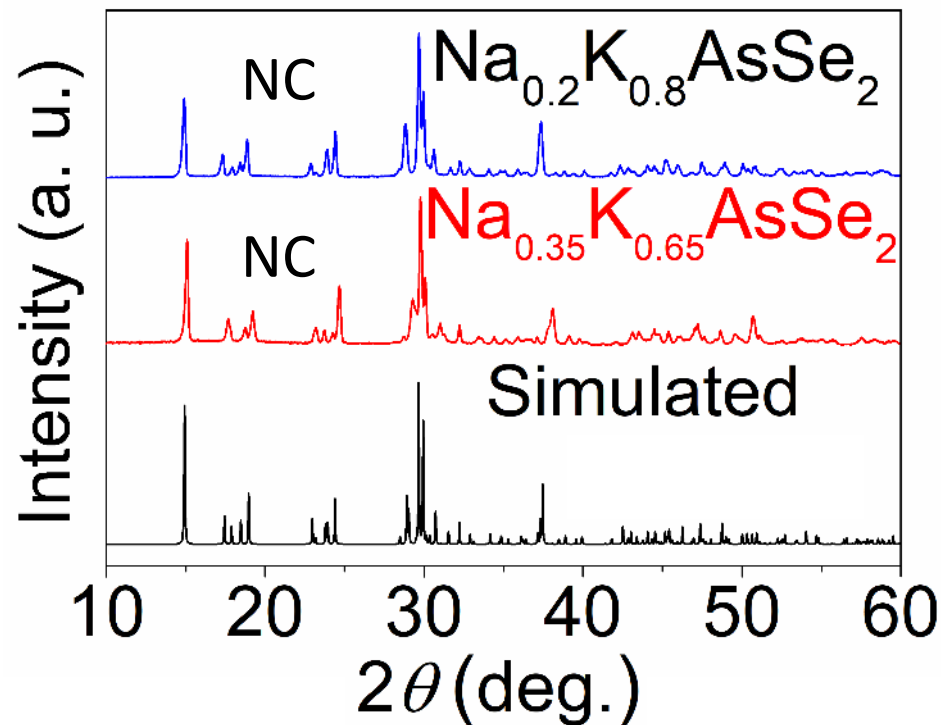
- The SHG intensity of powder LiAsS₂ is ~10 times larger than that of the benchmark AgGaSe₂ at 790 nm.
- The resulting Li_{0.6}Na_{0.4}AsS₂ is isostructural to LiAsS₂ and exhibits 30 times stronger SHG response than AgGaSe₂, a large enhancement over LiAsS₂ itself.
- We believe this enhancement is due to the small (fine tuning) of *Dimensional Reduction* occurring when larger Na is added raising the JDOS and enhancing the SHG.

Synthesis of $\text{Na}_{1-x}\text{K}_x\text{AsQ}_2$

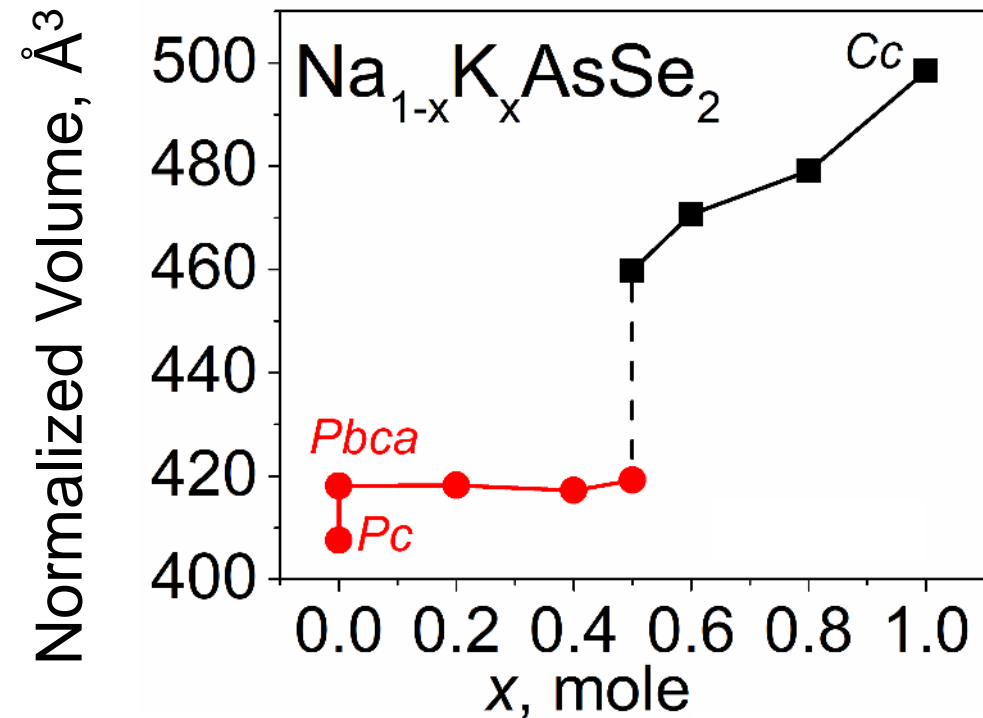
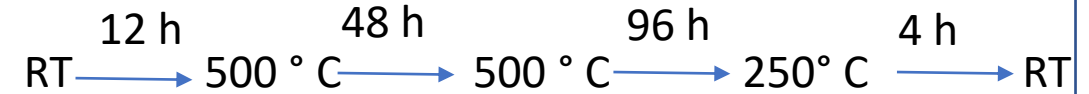


Similarly reactions were performed for $x = 0.65$ and 0.5 and $\text{Na}_{0.1}\text{K}_{0.9}\text{AsS}_2$

Powder XRD

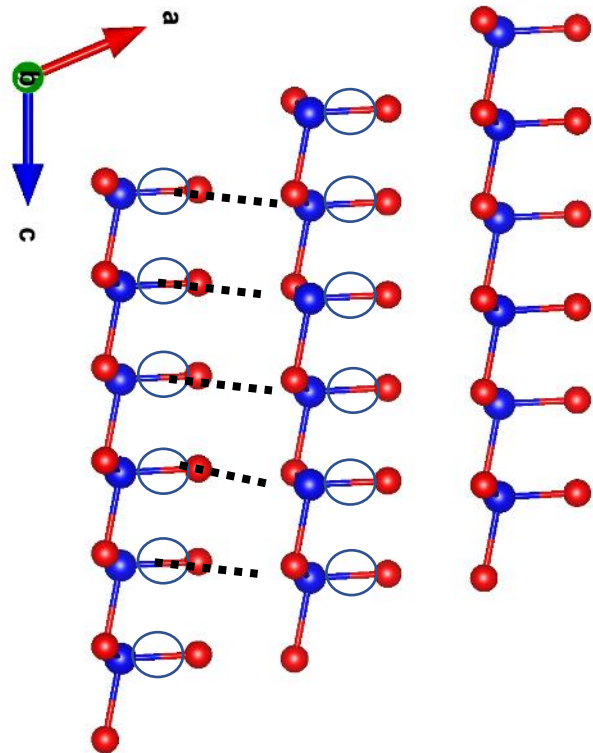


Standardized Temperature Profile

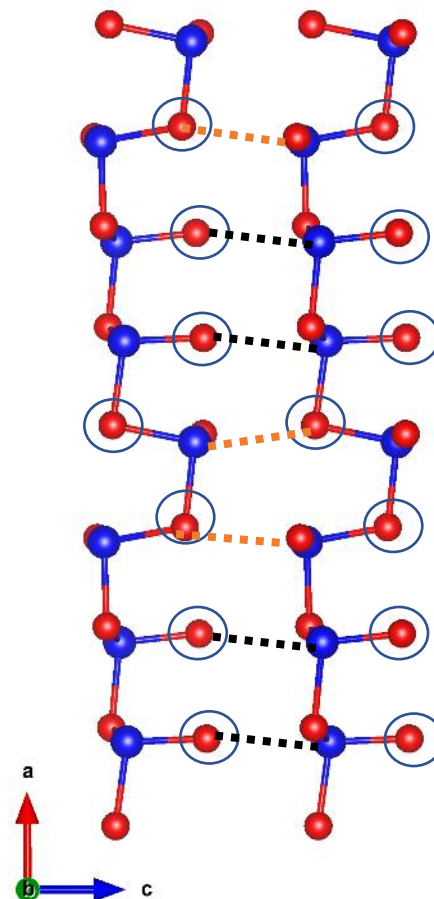


NC = noncentrosymmetric; C = centrosymmetric

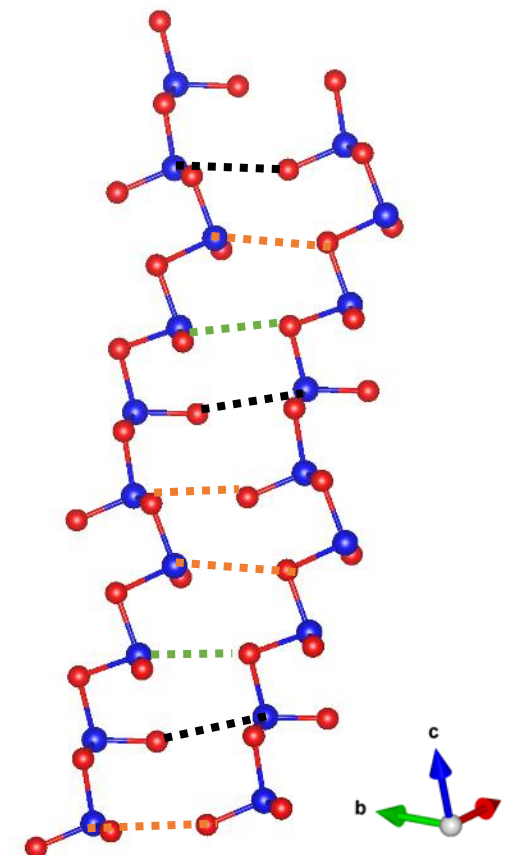
Change in interchain $[\text{AsQ}_2]^-$ interactions due to A cation



LiAsSe_2 (Cc)
Interchain distance
3.37 Å



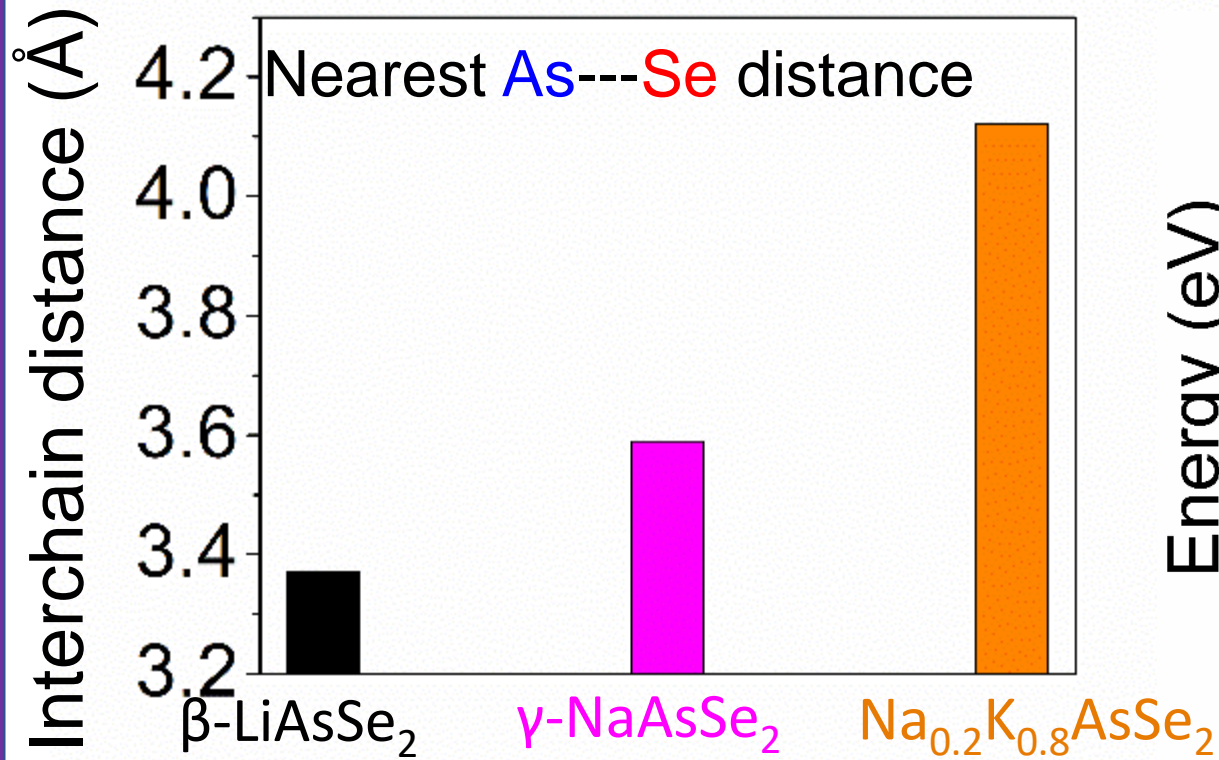
NaAsSe_2 (Pc)
Interchain distance
3.59 Å, 3.64 Å



$\text{Na}_{0.2}\text{K}_{0.8}\text{AsSe}_2$ (Cc)
Interchain distance
4.12 Å, 4.29 Å, 4.41 Å

As-Se Van der Waals distance ~ 4.64 Å

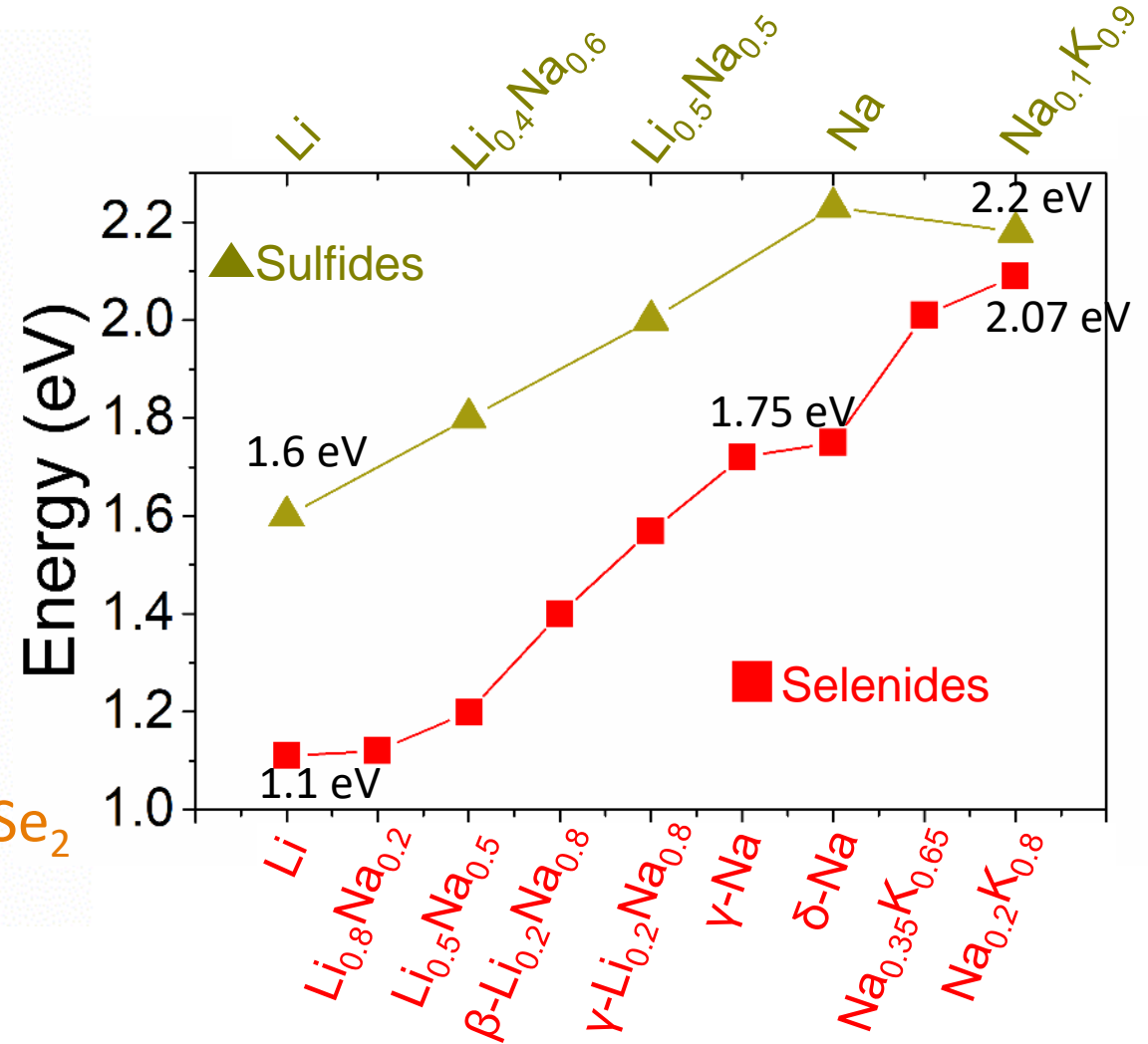
Bandgap comparison between AAsQ₂ structures



Experimental bandgap

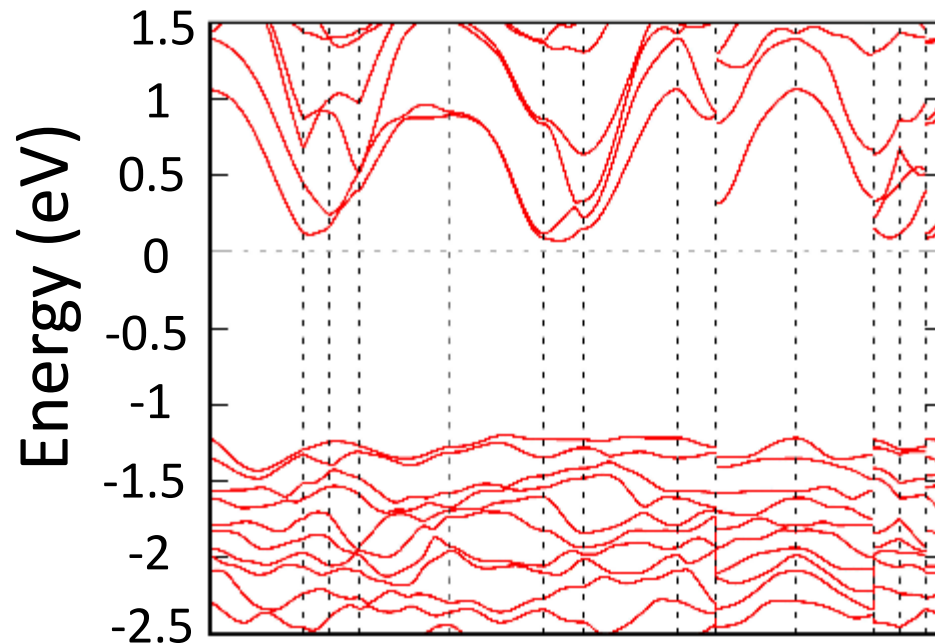
1.11 eV 1.75 eV 2.07 eV

LiAsSe₂ < γ -NaAsSe₂ < Na_{0.2}K_{0.8}AsSe₂



Bandgap increases when larger A cations are added

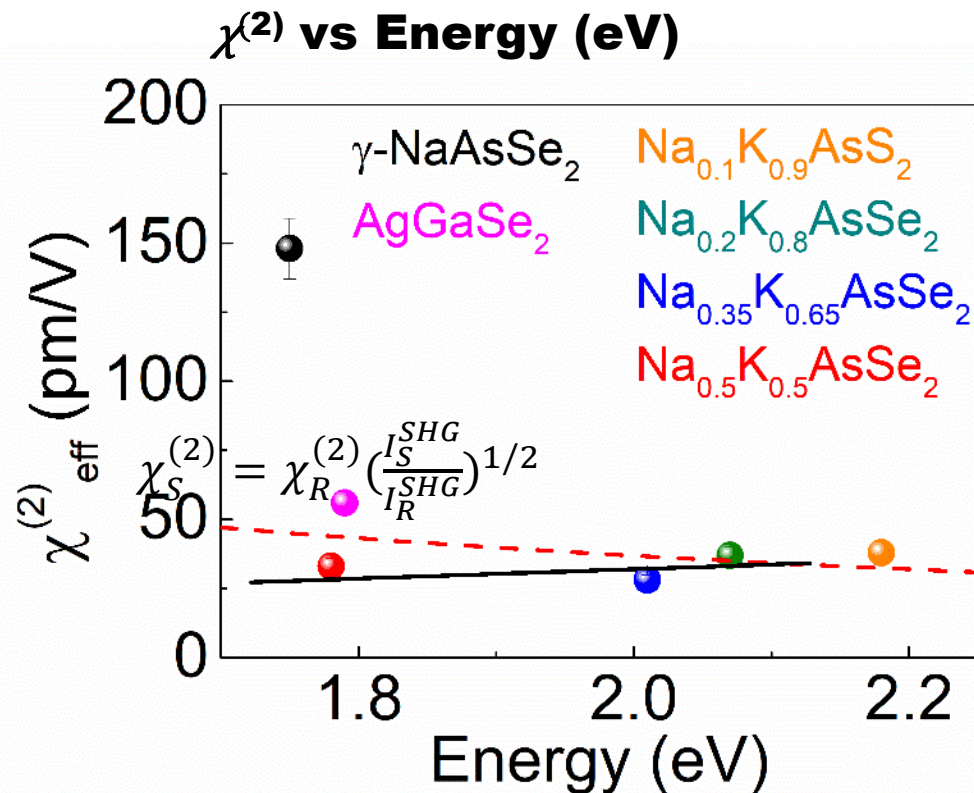
KAsSe₂ has flat bands like γ -NaAsSe₂ but γ -NaAsSe₂ has greater anisotropy along the chain direction



Effective mass direction	KAsSe ₂	γ -NaAsSe ₂
	Electrons	
a*	0.179 m ₀	0.219 m ₀
b*	0.154 m ₀	0.517 m ₀
c*	0.238 m ₀	4.961 m ₀
	Holes	
a*	0.820 m ₀	1.360 m ₀
b*	0.522 m ₀	2.159 m ₀
c*	0.715 m ₀	2.370 m ₀

γ -NaAsSe₂ has larger electron and hole mass along the chain direction.
 γ -NaAsSe₂ has flatter bands compared to KAsSe₂ and its analogous compounds.
 γ -NaAsSe₂ has greater anisotropy.

Low SHG response but high LIDT for $\text{Na}_{1-x}\text{K}_x\text{AsSe}_2$



Theoretical d_{ij}

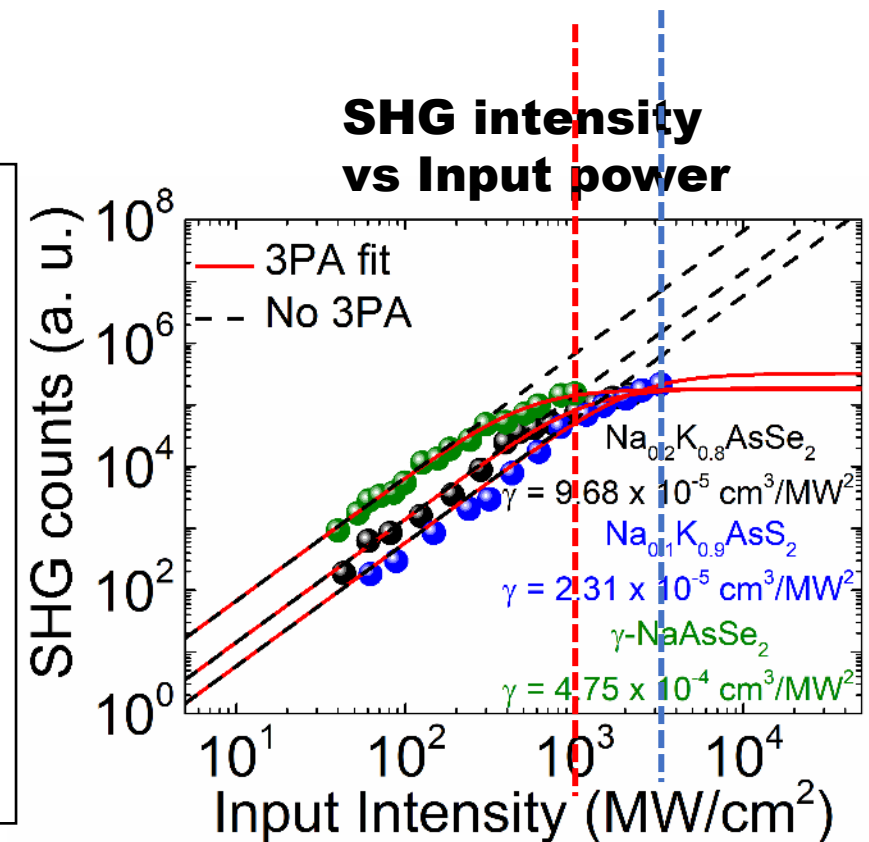
$\gamma\text{-NaAsSe}_2$
 $d_{11} = 168.9 \text{ pm/V}$

$\text{Na}_{0.5}\text{K}_{0.5}\text{AsSe}_2$
 $d_{26} = 48.3 \text{ pm/V}$

Experimental LIDT

$\gamma\text{-NaAsSe}_2$
 LIDT = 60 MW/cm^2

$\text{Na}_{0.2}\text{K}_{0.8}\text{AsSe}_2$
 LIDT = 303 MW/cm^2



All samples undergo 3 Photon Absorption (3PA)

$\chi_S^{(2)}$: SHG coefficient for the sample

$\chi_R^{(2)}$ SHG coefficient for the reference (AgGaSe_2)

Thanks to Hye Ryung Byun, Jang Group Sogang University for SHG measurements

Thanks to Michael J. Waters, Rondinelli Group Northwestern University for theoretical calculations

Grow Single crystal of NaAsSe₂

- Challenge:
- A phase transition from *Pc* to *Pbca* exists that may complicate our crystal growth efforts
- Approach: Understand the nature phase transition from *Pc* to *Pbca* and control it.

RESEARCH ARTICLE



Giant Non-Resonant Infrared Second Order Nonlinearity in γ -NaAsSe₂

Jingyang He, Abishek K. Iyer, Michael J. Waters, Sumanta Sarkar, Rui Zu, James M. Rondinelli, Mercuri G. Kanatzidis,* and Venkatraman Gopalan*

Infrared laser systems are vital for applications in spectroscopy, communications, and biomedical devices, where infrared nonlinear optical (NLO) crystals are required for broadband frequency down-conversion. Such crystals need to have high non-resonant NLO coefficients, a large bandgap, low absorption coefficient, and phase-matchability among other competing demands; for example, a larger bandgap leads to smaller NLO coefficients. Here, the successful growth of single crystals of γ -NaAsSe₂ that exhibit a giant second harmonic generation (SHG) susceptibility of $d_{11} = 590 \text{ pm V}^{-1}$ at $2 \mu\text{m}$ wavelength is reported; this is ~ 18 times larger than that of commercial AgGaSe₂ while retaining a similar bandgap of $\sim 1.87 \text{ eV}$, making it an outstanding candidate for quasi-phase-matched devices utilizing d_{11} . In addition, γ -NaAsSe₂ is both Type I and Type II phase-matchable, and has a transparency range up to $16 \mu\text{m}$ wavelength. Thus, γ -NaAsSe₂ is a promising bulk NLO crystal for infrared laser applications.

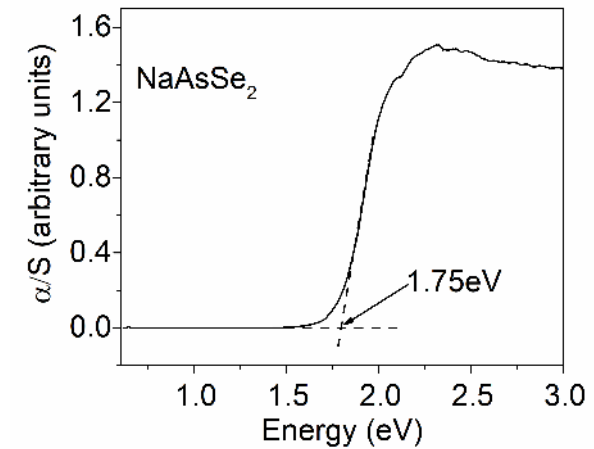
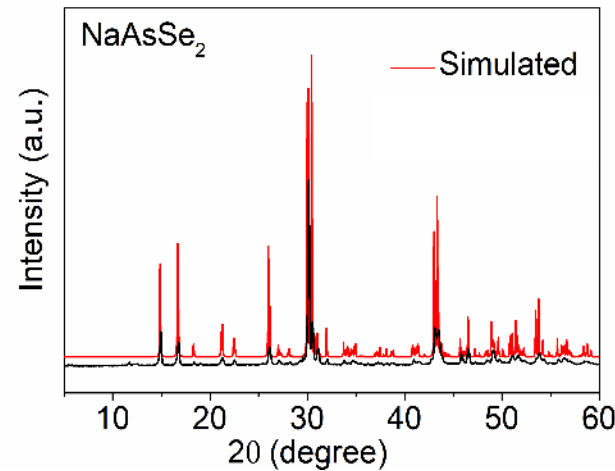
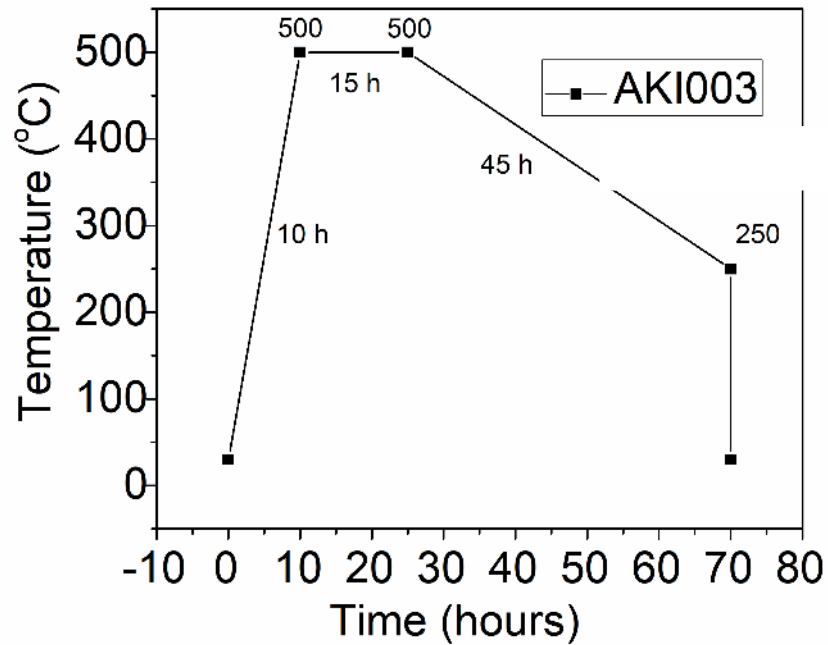
β -BaB₂O₄^[14] and LiNbO₃^[15] have been employed for generating light in the visible regime, they are not suitable for the infrared region because of their lower conversion efficiencies and infrared absorption past $4.5\text{--}5 \mu\text{m}$ wavelength. Although there are several new highly promising materials emerging from various research laboratories,^[16–18] currently only a few infrared NLO materials are commercially available such as AgGaSe₂^[19] AgGaSe₂^[20–22] and ZnGeP₂.^[23] A central goal of the laser materials community is to develop new NLO crystals to complement and improve upon the current commercial crystals. This is by no means an easy task, since there are many competing demands on NLO crystals: high nonlinear coefficients, large transparency range, and hence, a

Synthesis of γ -NaAsSe₂



Powder XRD

Optical absorption



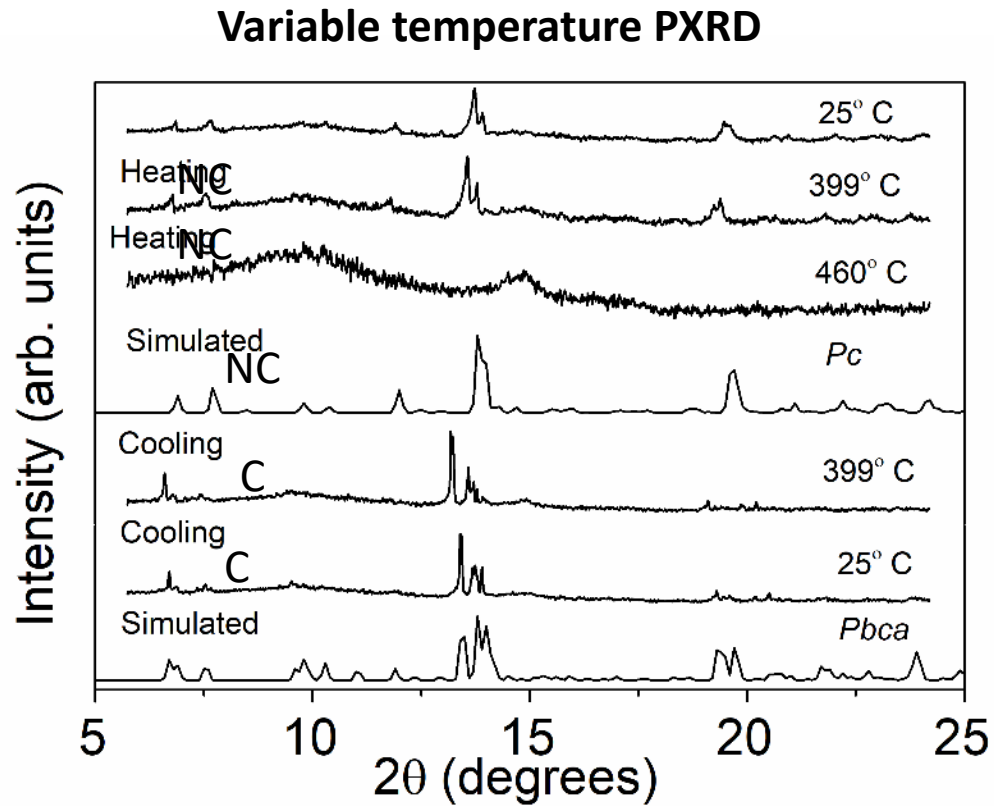
γ -NaAsSe₂, *Pc*
 melts congruently, melting point is 444 °C
Means large crystal growth possible

Structure information

Space Group: *Pc* (Non-centrosymmetric)
 $a = 11.682 \text{ \AA}$, $b = 5.9021 \text{ \AA}$, $c = 11.8231 \text{ \AA}$;
 $\beta = 90.446^\circ$
 Band gap: 1.75 eV

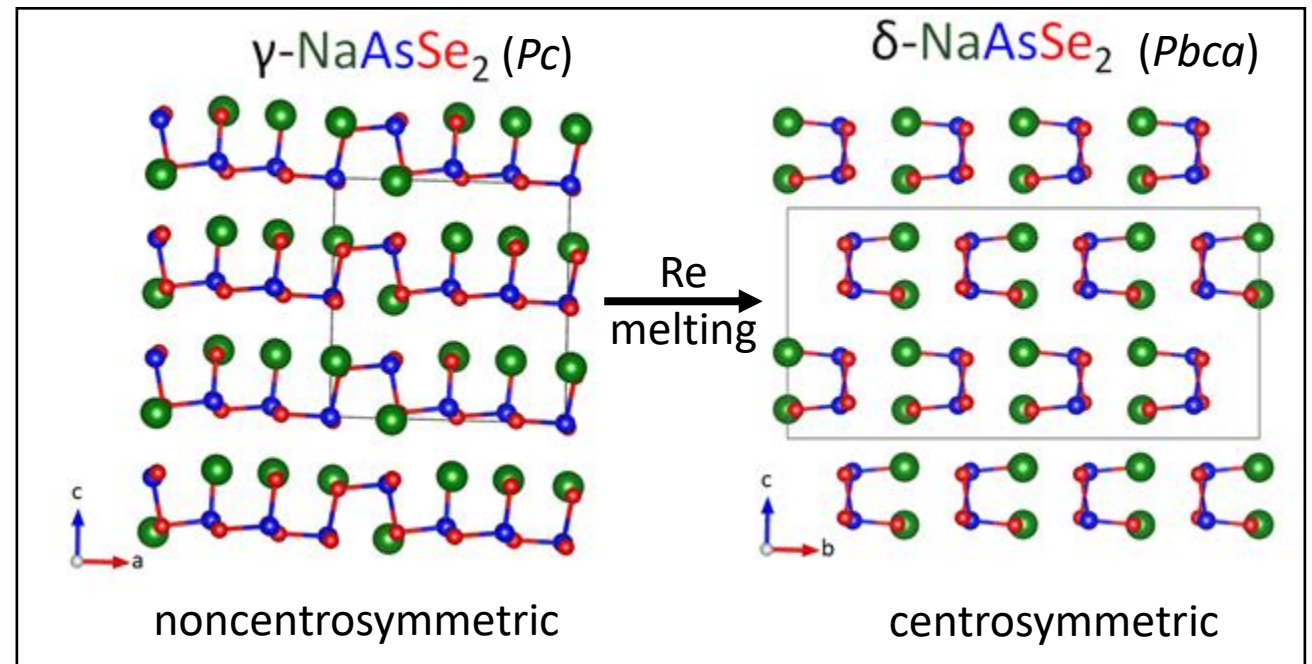
Challenge: Re-melting the γ -NaAsSe₂ (NC) sample changes to δ -NaAsSe₂ upon cooling

Synthetic Challenge: γ -NaAsSe₂ (NC) to δ -NaAsSe₂ (C) phase transition at 450°C



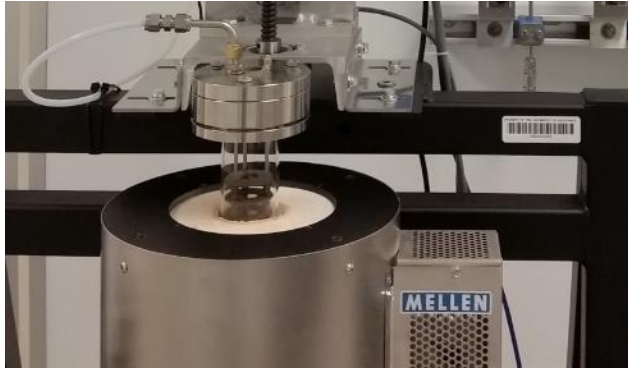
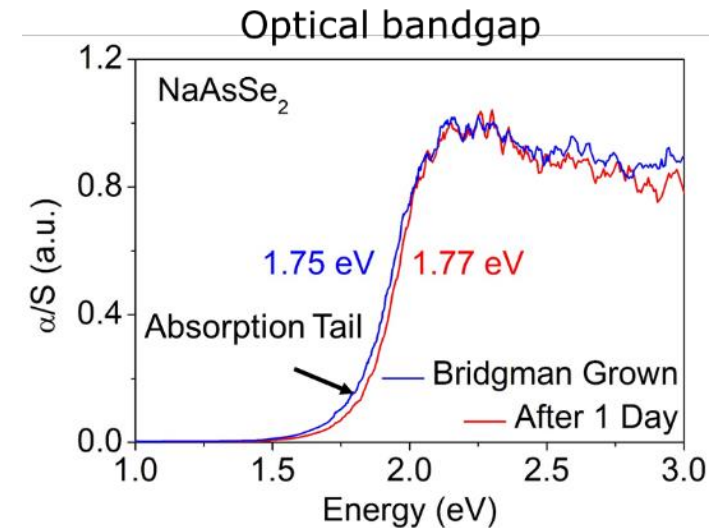
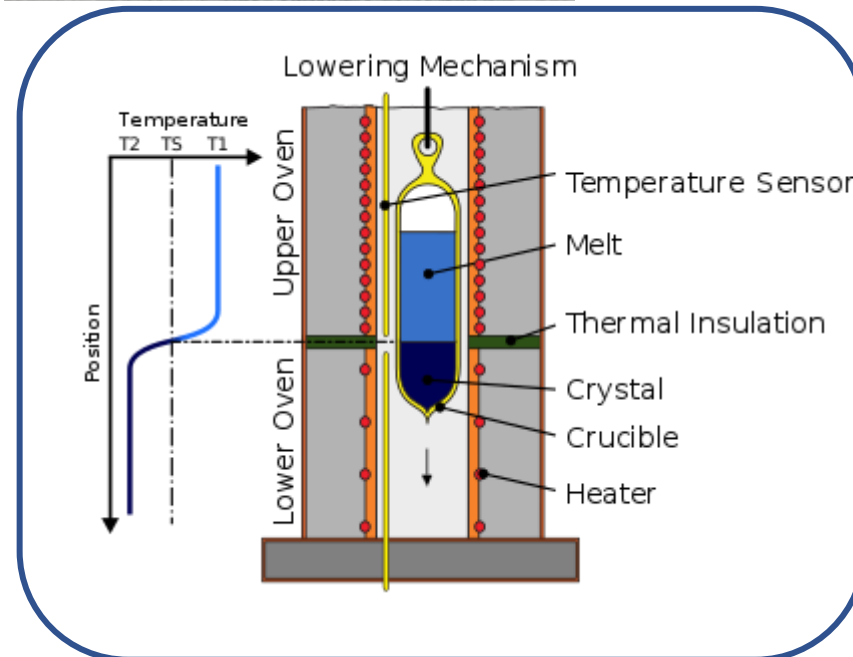
Ramp rate: 10°C/min, Mo K α

C = centrosymmetric
 NC = noncentrosymmetric



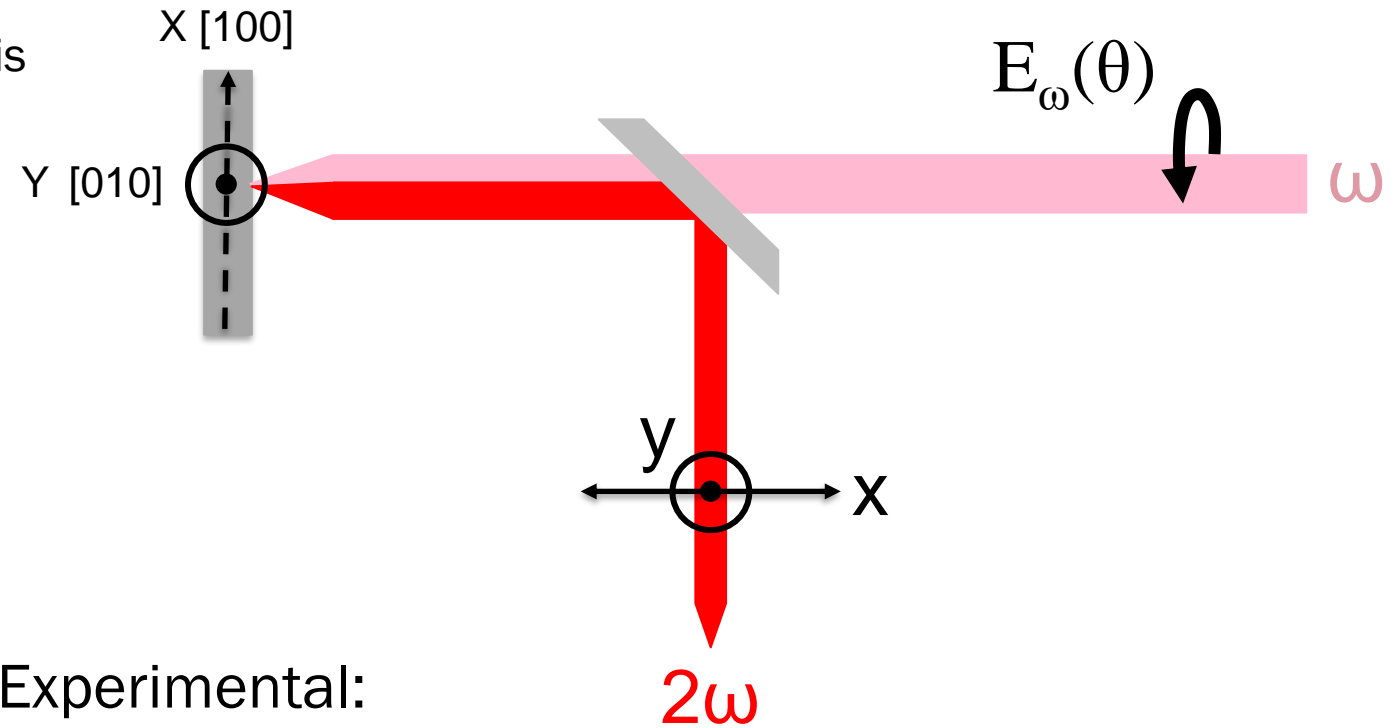
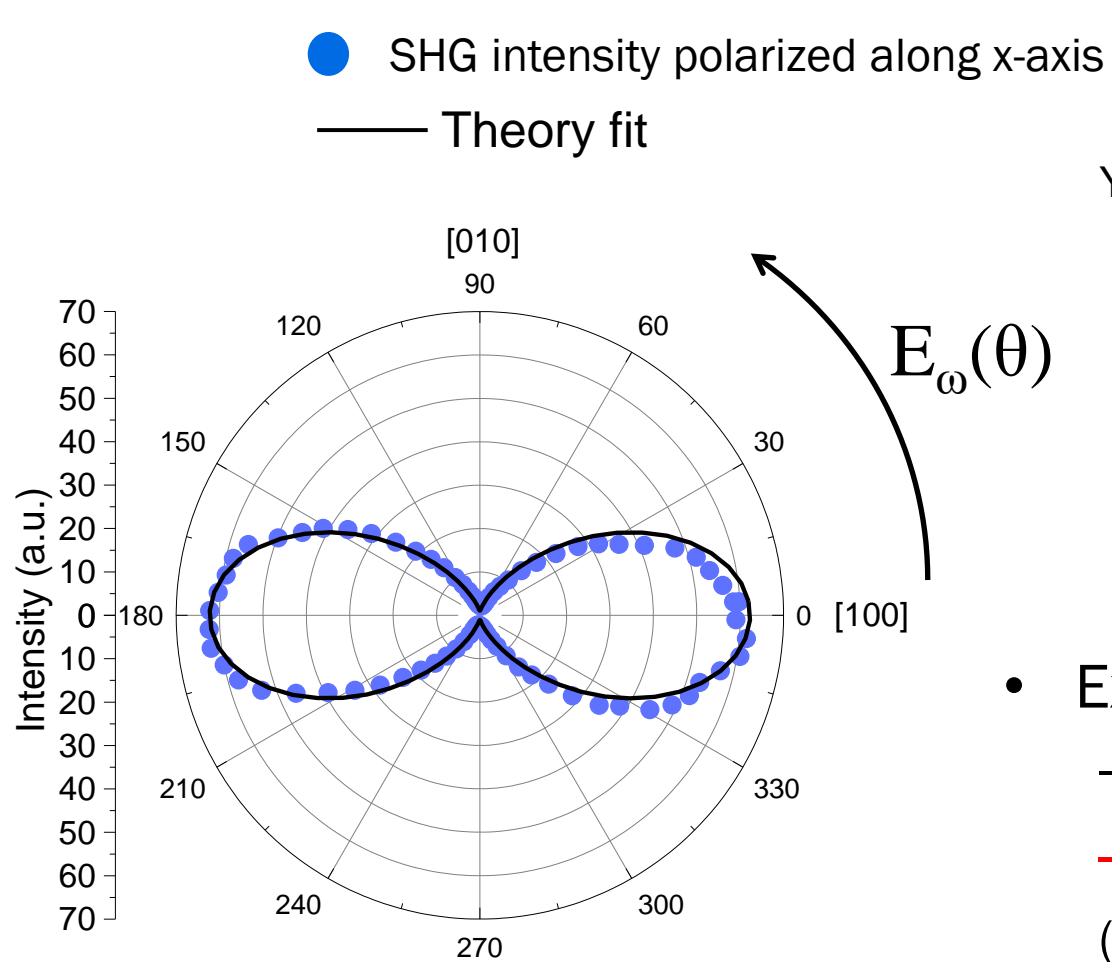
γ -NaAsSe₂ Single Crystals Grown by the Bridgman Method: first try

Bridgman furnace

Ingot of γ -NaAsSe₂Single Crystals of γ -NaAsSe₂

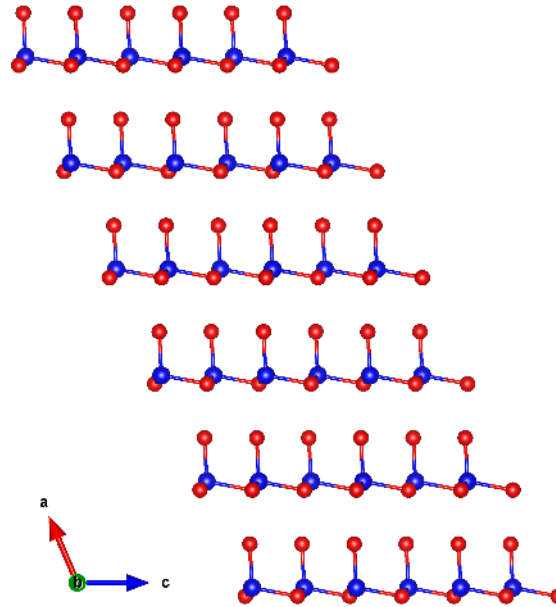
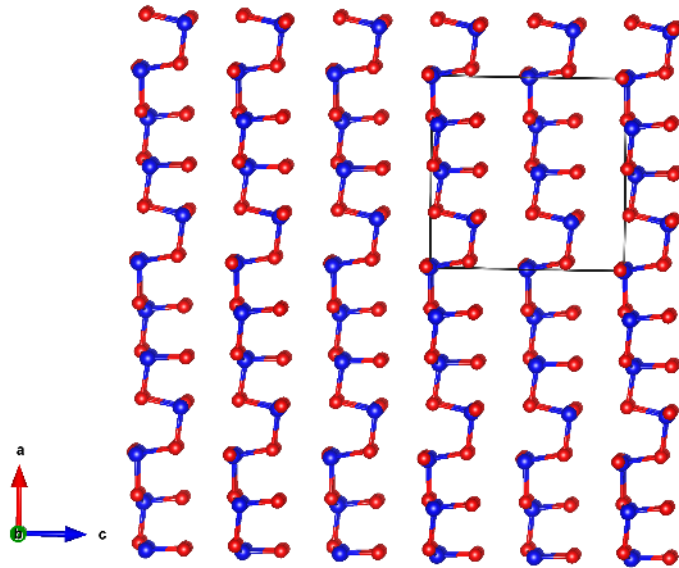
Temperature 520°C
Cold side: 300°C
Dropping rate: 0.5 mm/h

Nonlinear Optical Properties of γ -NaAsSe₂

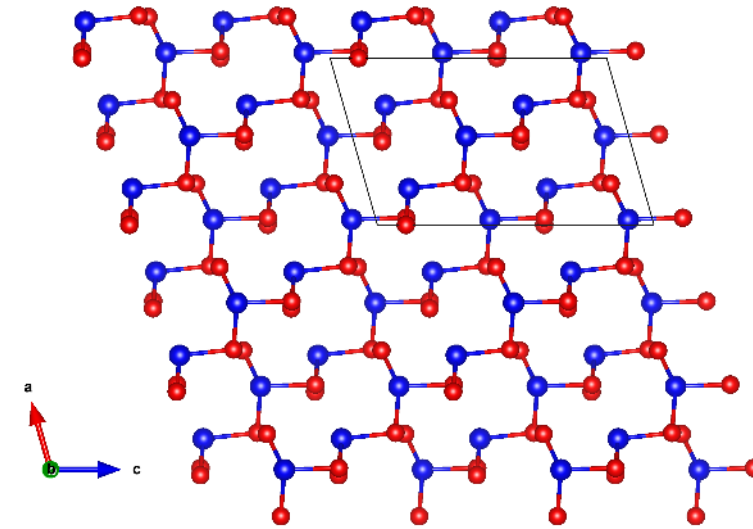


- Experimental:
 - $d_{11}/d_{12}=7.8$
 - $d_{11} \sim 354 \text{ pm/V}$ ($\chi^{(2)} = 2d_{11} \sim 708 \text{ pm/V}$)
 - (compared to LiNbO₃: $d_{33}=23.7 \text{ pm/V}$ at 1550nm)

How do we stabilize Cc γ -NaAsSe₂?



New structure type!



NaAsSe₂, Pc

$a = 11.682 \text{ \AA}$, $b = 5.902 \text{ \AA}$, $c = 11.823 \text{ \AA}$
 $\beta = 90.44^\circ$

LiAsSe₂, Cc

$a = 12.287 \text{ \AA}$, $b = 5.541 \text{ \AA}$, $c = 5.553 \text{ \AA}$
 $\beta = 113.12^\circ$

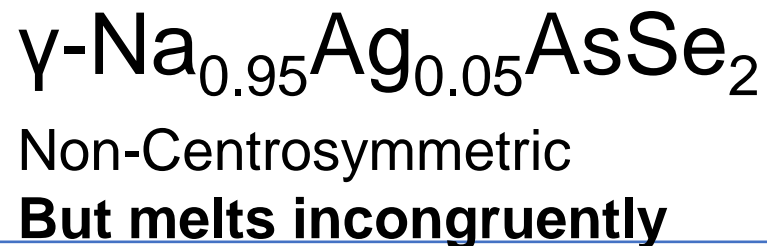
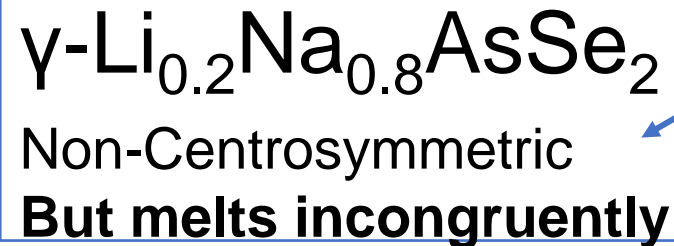
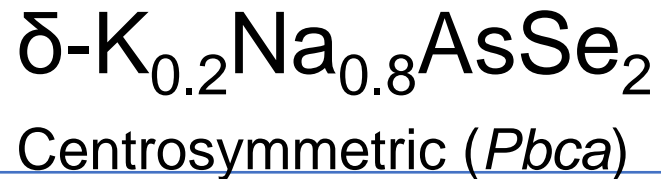
K_{0.8}Na_{0.2}AsSe₂, Cc

$a = 7.764 \text{ \AA}$, $b = 10.164 \text{ \AA}$,
 $c = 12.403 \text{ \AA}$, $\beta = 105.87^\circ$

Na, Li and K atoms removed, for a better understanding of the structures

Challenge: Can the γ -NaAsSe₂ be stabilized through chemical substitution?

Alkali-metal substitution

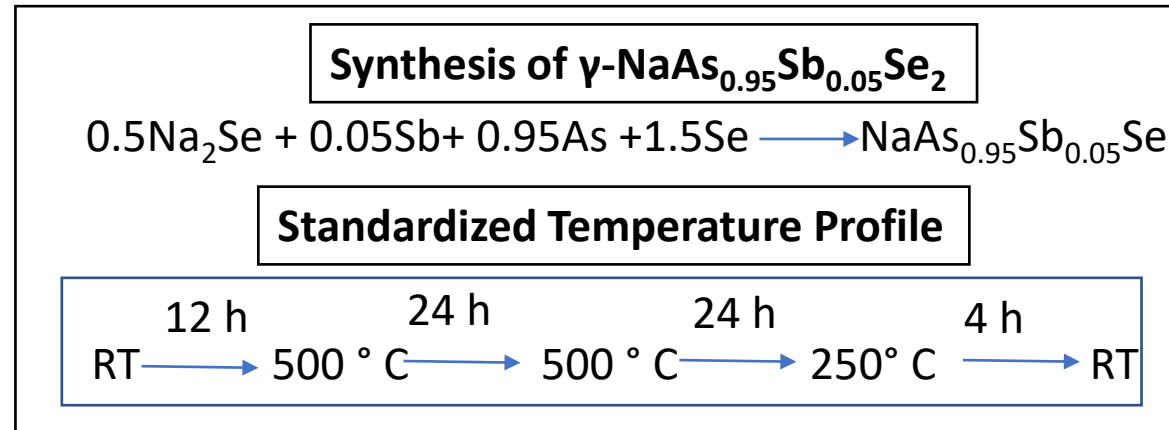


Chalcogen substitution

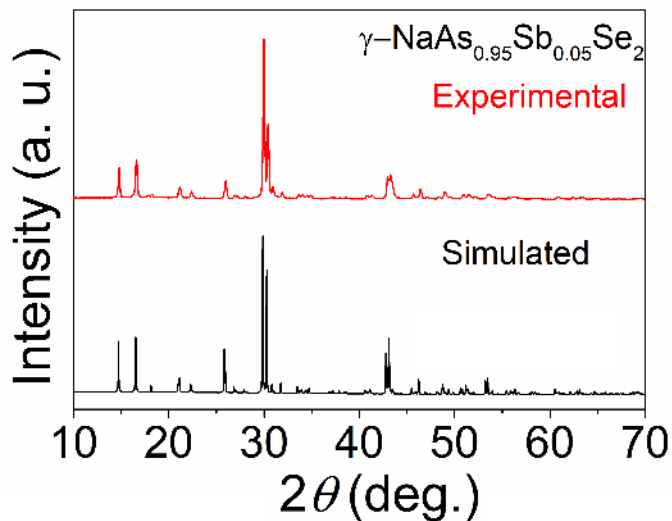


Sb substitution?

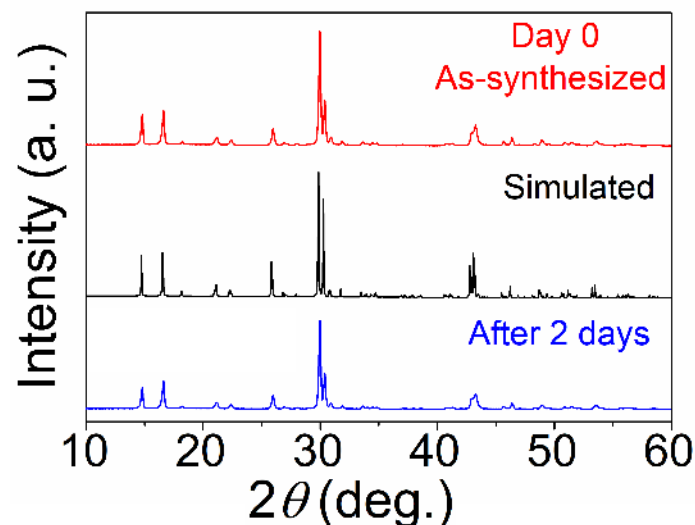
γ -NaAs_{0.95}Sb_{0.05}Se₂ crystallizes in γ -NaAsSe₂ (Pc)



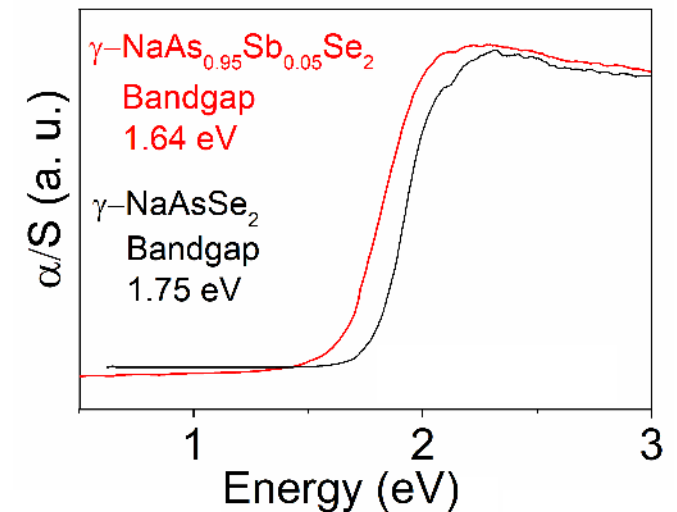
Powder x-ray diffraction



Sample stability in air

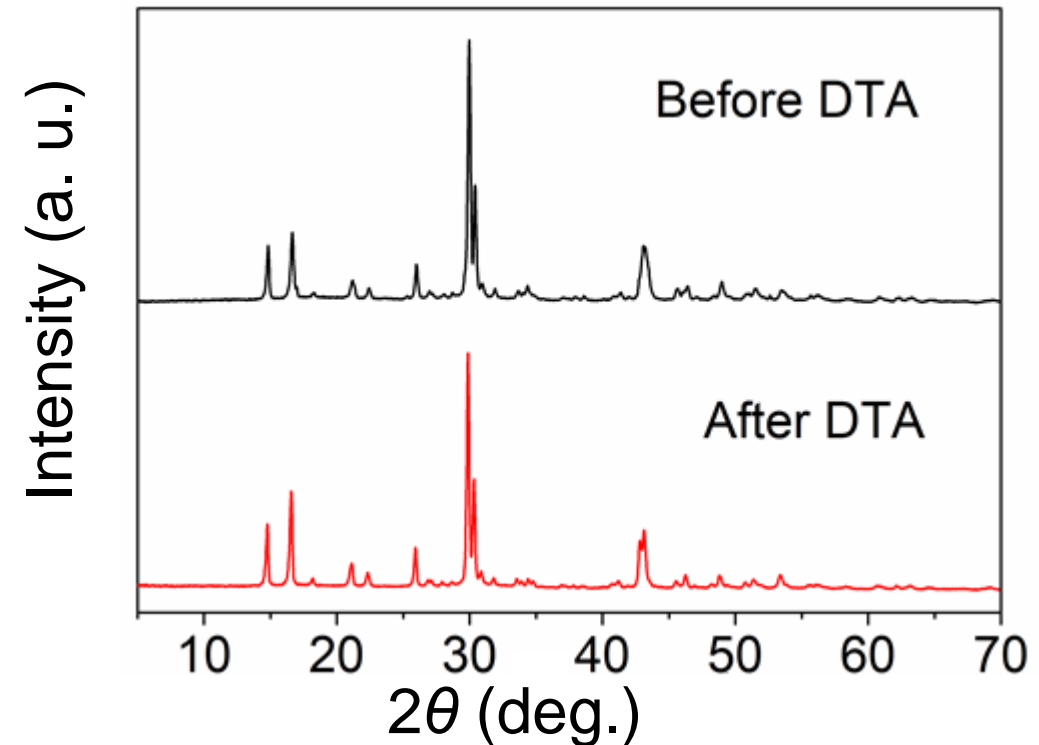
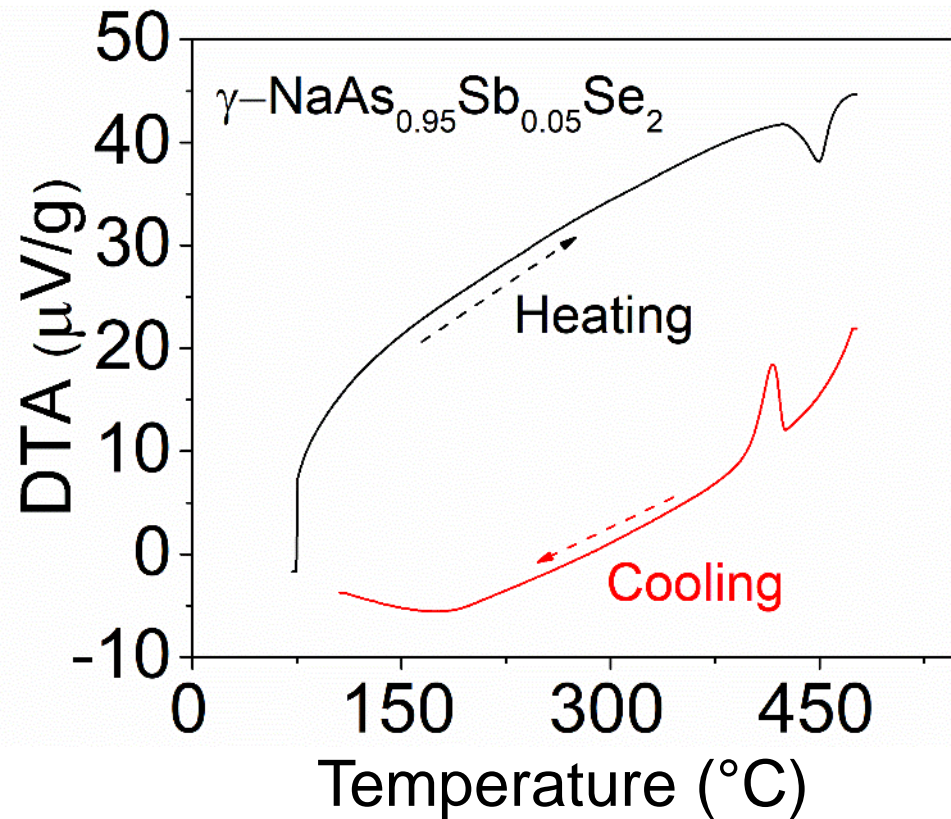


Diffuse Reflectance Spectrum



Differential Thermal Analysis confirms $\gamma\text{-NaAs}_{0.95}\text{Sb}_{0.05}\text{Se}_2$ remains noncentrosymmetric

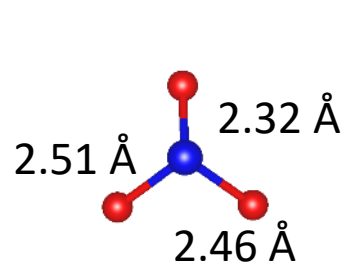
Good News!



$\gamma\text{-NaAsSe}_2$ is stabilized by doping with Sb

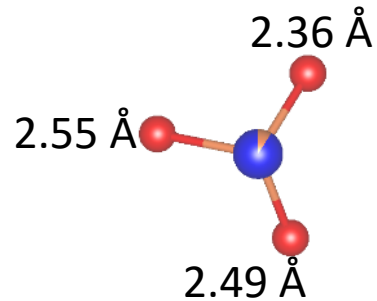
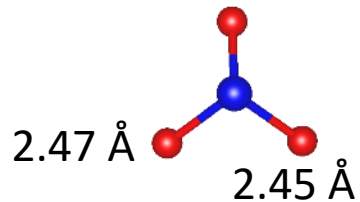
As-Se bond length in the different $AAsSe_2$ structures

Substitution of As with Sb offers bond flexibility to keep the chain

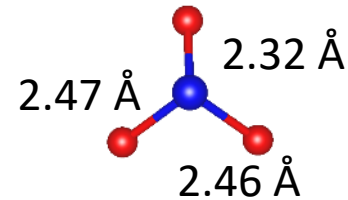


Melts
incongruently

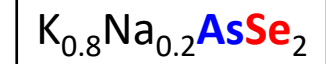
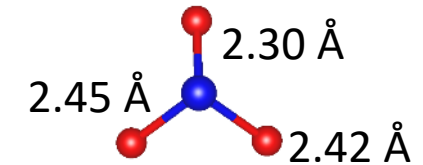
2.29 Å



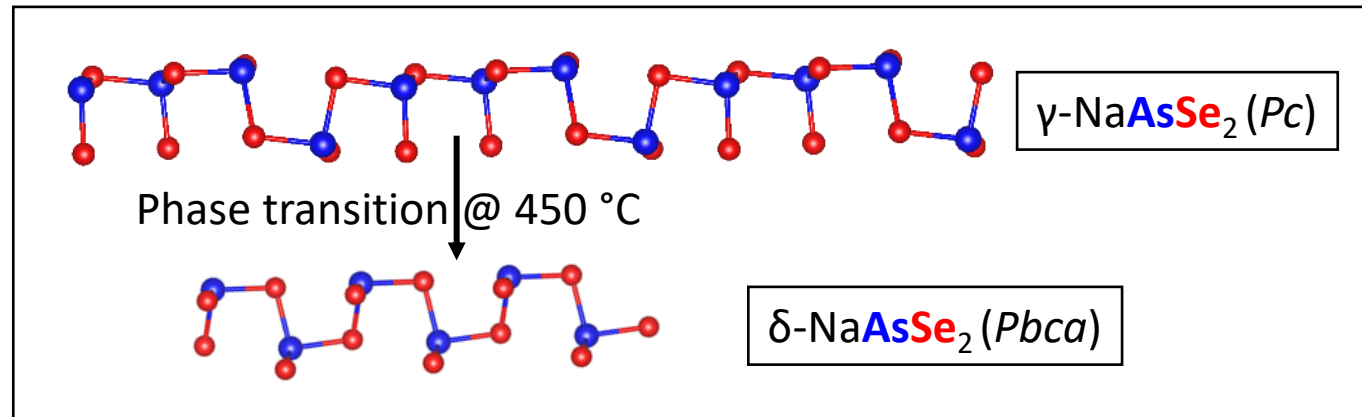
Melts
congruently



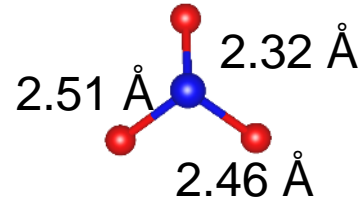
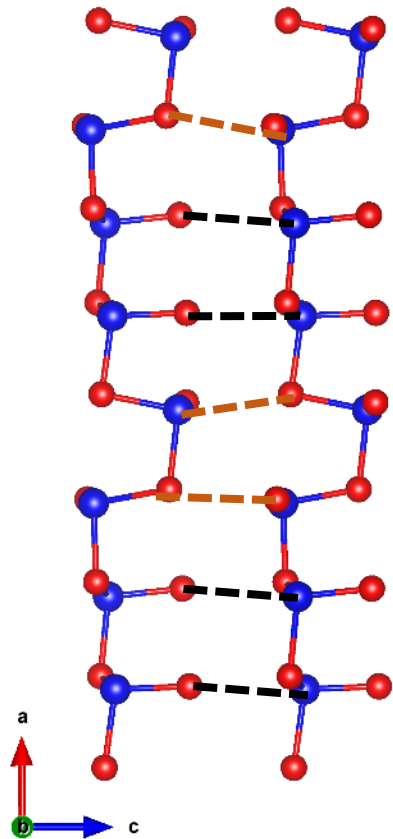
Melts
congruently



Melts
congruently



Structural differences between γ -NaAsSe₂ and NaAs_{0.95}Sb_{0.05}Se₂

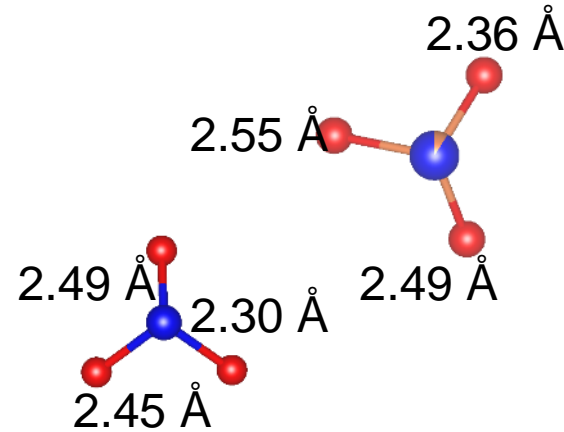


γ -NaAsSe₂
Space Group: *Pc*

$a = 11.726(2) \text{ \AA}$
 $b = 5.932(1) \text{ \AA}$
 $c = 11.866(2) \text{ \AA}$
 $\beta = 90.39(3)^\circ$

V: 825.5 (3) \AA^3

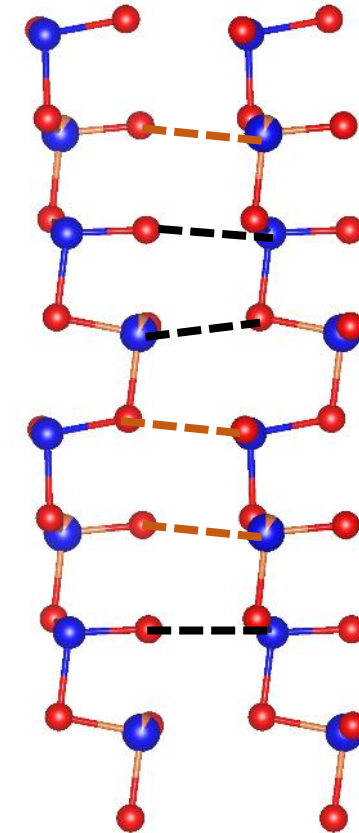
γ -NaAsSe₂ (*Cc*)
Interchain distance
3.59 \AA , 3.64 \AA



NaAs_{0.95}Sb_{0.05}Se₂
Space Group: *Pc*

$a = 11.761(2) \text{ \AA}$
 $b = 5.958(7) \text{ \AA}$
 $c = 11.928(2) \text{ \AA}$
 $\beta = 90.34(3)^\circ$

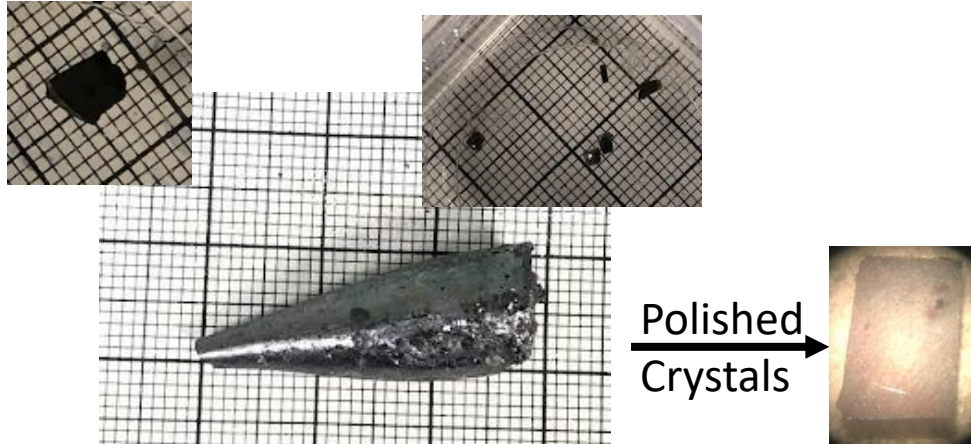
V: 835.9 (3) \AA^3



γ -NaAs_{0.95}Sb_{0.05}Se₂ (*Cc*)
Interchain distance
3.63 \AA , 3.67 \AA

Bridgman growth of $\gamma\text{-NaAs}_{0.95}\text{Sb}_{0.05}\text{Se}_2$

5mm x 4mm x 2mm



Polished
Crystals

Temperature 520°C

Cold side: 350°C

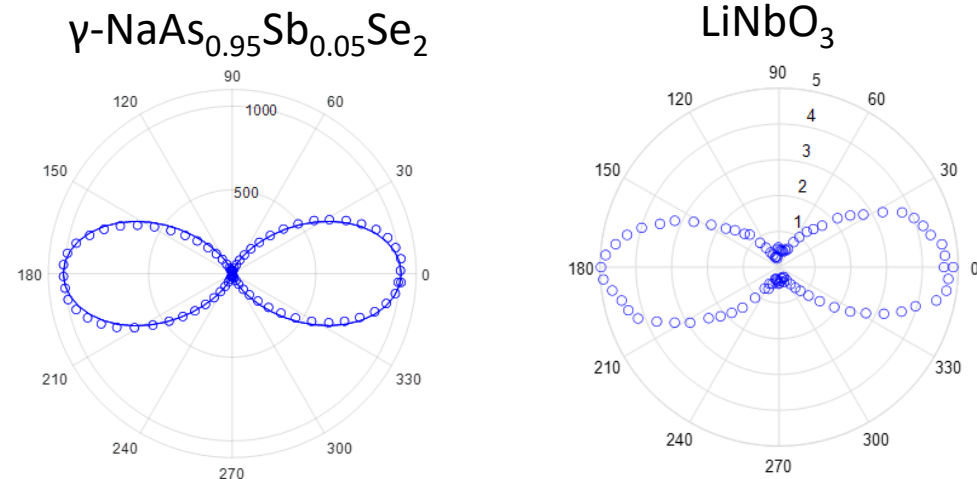
Dropping rate: 1 mm/h

Kept at 350 °C for 54 hours

Dropped to RT at 10 mm/h

Purity of the starting material
3N Na₂Se, 5N As, 5N Sb and 5N Se

Preliminary SHG data at 2 μm on the single crystal of
 $\gamma\text{-NaAs}_{0.95}\text{Sb}_{0.05}\text{Se}_2$

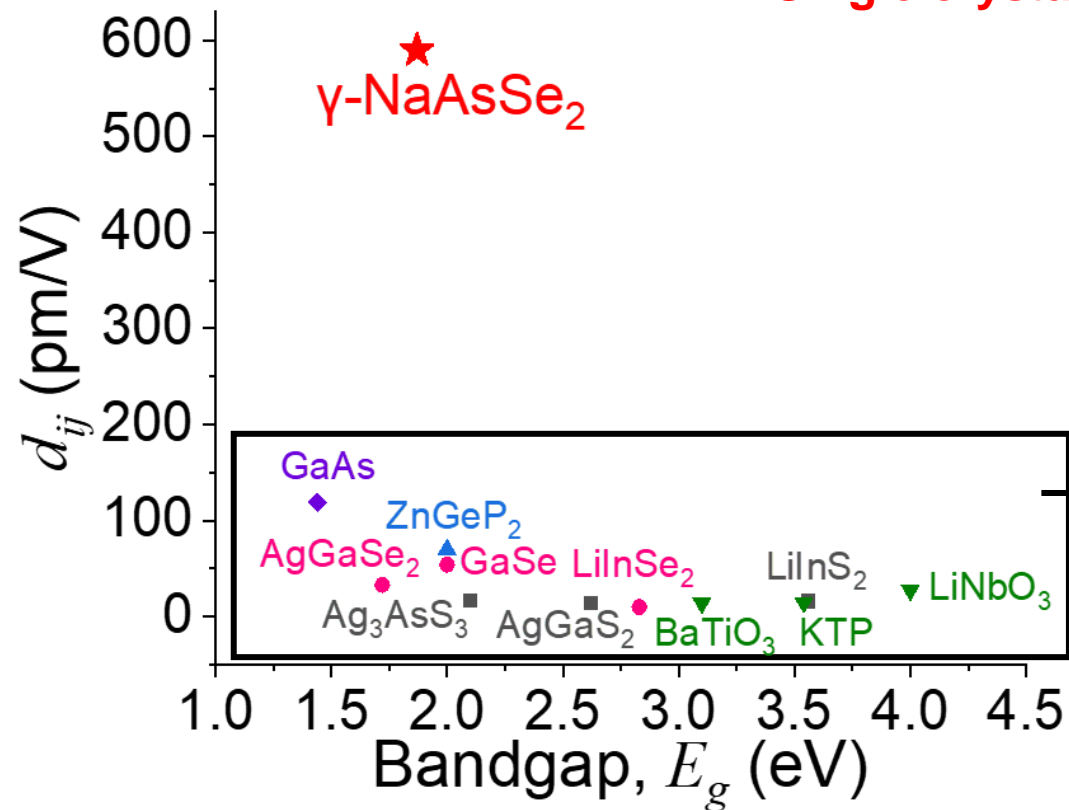


LiNbO₃ d_{33} : 18 pm/V
 $\gamma\text{-NaAs}_{0.95}\text{Sb}_{0.05}\text{Se}_2$ d_{11} : 592 pm/V

The SHG data is comparable to
 $\gamma\text{-NaAsSe}_2$

Comparison of γ -NaAsSe₂ with other NLO materials

Single crystal of γ -NaAsSe₂ has a $d_{11} = 590$ pm/V @ 2 μ m



Comparison with SHG response to all other commercially used NLO crystals

AgGaSe₂: d_{36} : 33 pm/V (2 μ m)

ZnGeP₂: d_{36} : 75 pm/V (2 μ m)

These results clearly suggest that stabilizing the γ -NaAsSe₂ is worth exciting!